

TLV225x-EP, TLV225xA-EP Advanced LinCMOS™ RAIL-TO-RAIL VERY-LOW-POWER OPERATIONAL AMPLIFIERS

SGLS217B – NOVEMBER 2003 – REVISED JUNE 2006

- **Controlled Baseline**
 - One Assembly/Test Site, One Fabrication Site
- **Extended Temperature Performance of -40°C to 125°C**
- **Enhanced Diminishing Manufacturing Sources (DMS) Support**
- **Enhanced Product-Change Notification**
- **Qualification Pedigree†**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 150 V (TLV2252/52A) and 100 V (TLV2254/54A) Using Machine Model (C = 200 pF, R = 0)**

† Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.

- **Output Swing Includes Both Supply Rails**
- **Low Noise . . . 19 nV/ $\sqrt{\text{Hz}}$ Typ at $f = 1 \text{ kHz}$**
- **Low Input Bias Current . . . 1 pA Typ**
- **Fully Specified for Both Single-Supply and Split-Supply Operation**
- **Very Low Power . . . 34 μA Per Channel (Typ)**
- **Common-Mode Input Voltage Range Includes Negative Rail**
- **Low Input Offset Voltage: 850 μV Max at $T_A = 25^{\circ}\text{C}$**
- **Wide Supply Voltage Range: 2.7 V to 16 V**
- **Macromodel Included**

description/ordering information

The TLV2252 and TLV2254 are dual and quadruple low-voltage operational amplifiers from Texas Instruments. Both devices exhibit rail-to-rail output performance for increased dynamic range in single- or split-supply applications. The TLV225x family consumes only 34 μA of supply current per channel. This micropower operation makes them good choices for battery-powered applications. This family is fully characterized at 3 V and 5 V and is optimized for low-voltage applications. The noise performance has been dramatically improved over previous generations of CMOS amplifiers. The TLV225x has a noise level of 19 nV/ $\sqrt{\text{Hz}}$ at 1kHz, four times lower than competitive micropower solutions.

The TLV225x, exhibiting high input impedance and low noise, are excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single or split supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs). For precision applications, the TLV225xA family is available and has a maximum input offset voltage of 850 μV .

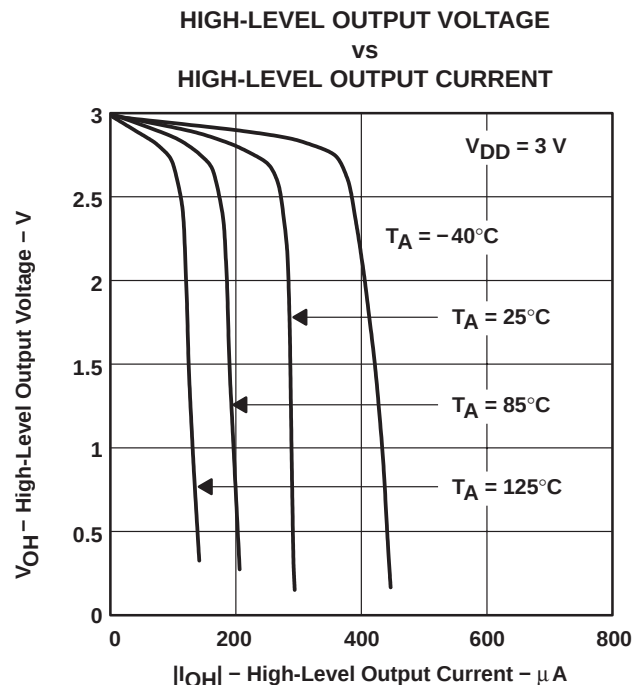


Figure 1



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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description/ordering information (continued)

The TLV2252/2254 also make great upgrades to the TLV2322/2424 in standard designs. They offer increased output dynamic range, lower noise voltage, and lower input offset voltage. This enhanced feature set allows them to be used in a wider range of applications. For applications that require higher output drive and wider input voltage range, see the TLV2432 and TLV2442 devices. If your design requires single amplifiers, please see the TLV2211/21/31 family. These devices are single rail-to-rail operational amplifiers in the SOT-23 package. Small size and low power consumption make them ideal for high density, battery-powered equipment.

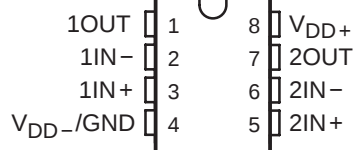
ORDERING INFORMATION

T _A	V _{IO} max AT 25°C	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 125°C	850 µV	SOIC (D)	Tape and reel	TLV2252AQDREP	2252AE
		TSSOP (PW)	Tape and reel	TLV2252AQPWREP†	
	1500 µV	SOIC (D)	Tape and reel	TLV2252QDREP	2252EP
		TSSOP (PW)	Tape and reel	TLV2252QPWREP†	
	850 µV	SOIC (D)	Tape and reel	TLV2254AQDREP	TLV2254AEP
		TSSOP (PW)	Tape and reel	TLV2254AQPWREP†	
	1500 µV	SOIC (D)	Tape and reel	TLV2254QDREP	TLV2254EP
		TSSOP (PW)	Tape and reel	TLV2254QPWREP†	

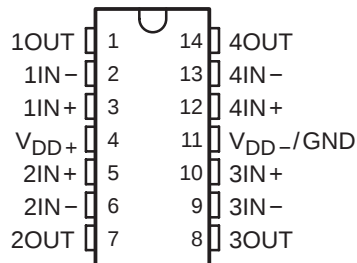
† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

Product preview

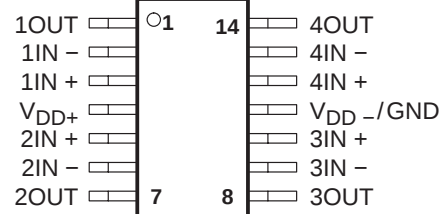
TLV2252, TLV2252A
D OR PW PACKAGE
(TOP VIEW)



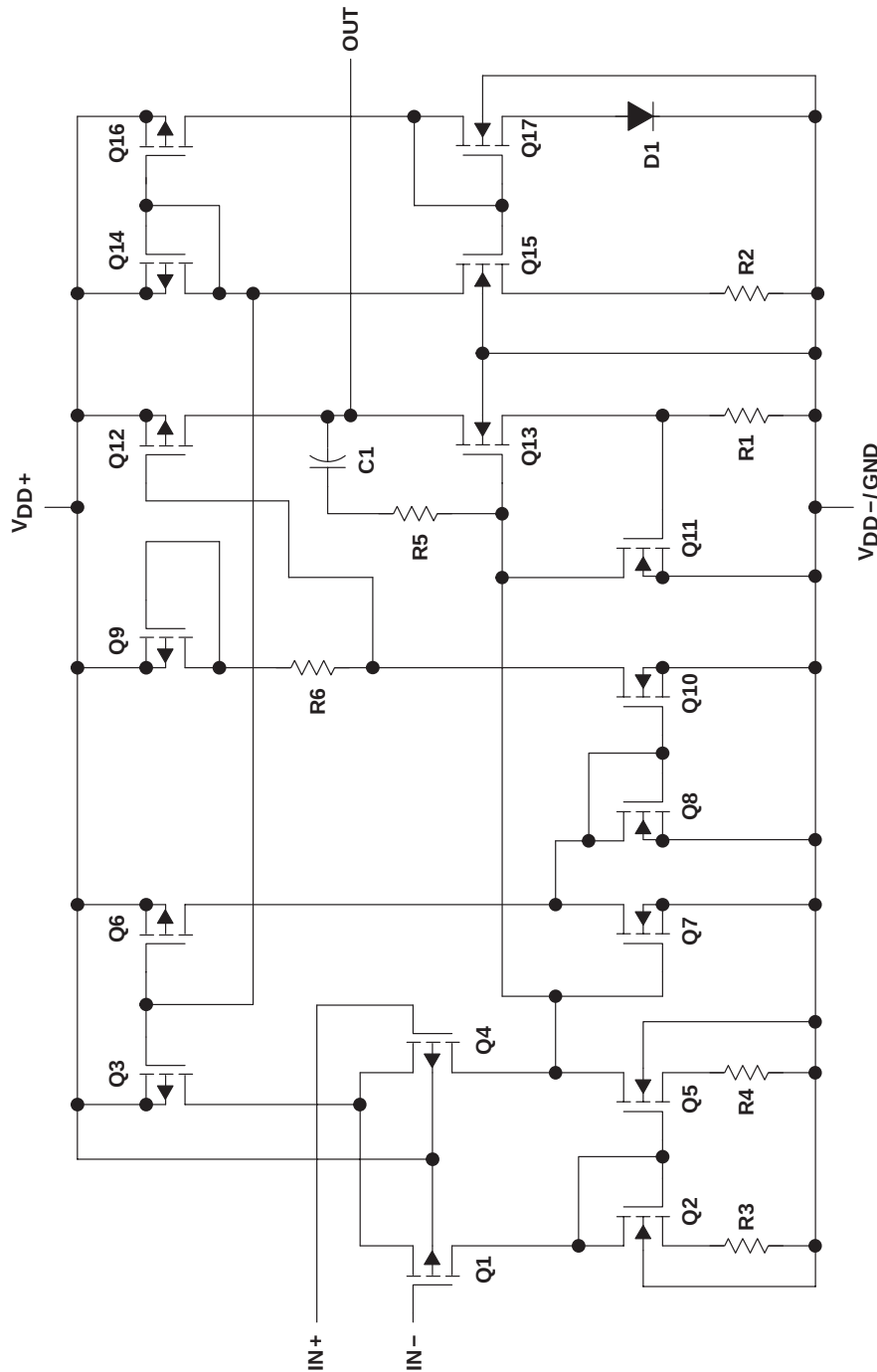
TLV2254, TLV2254A
D PACKAGE
(TOP VIEW)



TLV2254, TLV2254A
PW PACKAGE
(TOP VIEW)



equivalent schematic (each amplifier)



ACTUAL DEVICE COMPONENT COUNT†		
COMPONENT	TLV2252	TLV2254
Transistors	38	76
Resistors	30	56
Diodes	9	18
Capacitors	3	6

† Includes both amplifiers and all ESD, bias, and trim circuitry

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V_{DD} (see Note 1)	16 V
Differential input voltage, V_{ID} (see Note 2)	$\pm V_{DD}$
Input voltage range, V_I (any input, see Note 1)	$V_{DD-} - 0.3 \text{ V}$ to V_{DD+}
Input current, I_I (each input)	$\pm 5 \text{ mA}$
Output current, I_O	$\pm 50 \text{ mA}$
Total current into V_{DD+}	$\pm 50 \text{ mA}$
Total current out of V_{DD-}	$\pm 50 \text{ mA}$
Duration of short-circuit current (at or below 25°C) (see Note 3)	Unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A	-40°C to 125°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1,6 mm (1/16 in) from case for 10 s	260°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD-} .
2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below $V_{DD-} - 0.3 \text{ V}$.
3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
D-8	725 mW	5.8 mW/°C	377 mW	145 mW
D-14	950 mW	7.6 mW/°C	494 mW	190 mW
PW-8	525 mW	4.2 mW/°C	273 mW	105 mW
PW-14	700 mW	5.6 mW/°C	364 mW	140 mW

recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V_{DD} (see Note 1)	2.7	8	V
Input voltage range, V_I	V_{DD-}	$V_{DD+} - 1.3$	V
Common-mode input voltage, V_{IC}	V_{DD-}	$V_{DD+} - 1.3$	V
Operating free-air temperature, T_A	-40	125	°C

NOTE 1: All voltage values, except differential voltages, are with respect to V_{DD-} .

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TLV2252 electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2252			TLV2252A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} \pm \pm 1.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C		200	1500		200	850	μV
		Full range			1750			1000	
α_{VIO} Temperature coefficient of input offset voltage	$V_{DD} \pm \pm 1.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C to 85°C		0.5			0.5		$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)	$V_{DD} \pm \pm 1.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C		0.003			0.003		$\mu\text{V}/\text{mo}$
I_{IO} Input offset current	$V_{DD} \pm \pm 1.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C		0.5	60		0.5	60	pA
		125°C			1000			1000	
I_{IB} Input bias current	$V_{DD} \pm \pm 1.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C		1	60		1	60	pA
		125°C			1000			1000	
V_{ICR} Common-mode input voltage range	$R_S = 50\ \Omega$, $ V_{IO} \leq 5\text{ mV}$	25°C	0 to 2	-0.3 to 2.2		0 to 2	-0.3 to 2.2		V
		Full range	0 to 1.7			0 to 1.7			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C		2.98			2.98		V
	$I_{OH} = -75\ \mu\text{A}$			2.9			2.9		
	$I_{OH} = -150\ \mu\text{A}$	Full range		2.8			2.8		
V_{OL} Low-level output voltage	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$	25°C		10			10		mV
	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$			100	150		100	150	
		Full range			165			165	
	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C		200	300		200	300	
		Full range			300			300	
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 1.5\text{ V}$, $V_O = 1\text{ V to }2\text{ V}$	$R_L = 100\text{ k}\Omega^\ddagger$	25°C	100	250		100	250	V/mV
			Full range		10		10		
		$R_L = 1\text{ M}\Omega^\ddagger$	25°C		800			800	
$r_{i(d)}$ Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$ Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$c_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}$	25°C		8			8		pF
z_o Closed-loop output impedance	$f = 25\text{ kHz}$, $A_V = 10$	25°C		220			220		Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }1.7\text{ V}$, $V_O = 1.5\text{ V}$, $R_S = 50\ \Omega$	25°C	65	75		65	77		dB
		Full range		60			60		
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{DD} / \Delta V_{IO}$)	$V_{DD} = 2.7\text{ V to }8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C	80	95		80	100		dB
		Full range		80			80		
I_{DD} Supply current	$V_O = 1.5\text{ V}$, No load	25°C		68	125		68	125	μA
		Full range			150			150	

† Full range is -40°C to 125°C .

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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TLV2252 operating characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2252			TLV2252A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
SR Slew rate at unity gain	$V_O = 0.8\text{ V to }1.4\text{ V}, R_L = 100\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C	0.07	0.1		0.07	0.1		V/ μs
		Full range	0.05			0.05			
V_n Equivalent input noise voltage	$f = 10\text{ Hz}$	25°C		35			35		nV/ $\sqrt{\text{Hz}}$
	$f = 1\text{ kHz}$			19			19		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz to }1\text{ Hz}$	25°C		0.6			0.6		μV
	$f = 0.1\text{ Hz to }10\text{ Hz}$			1.1			1.1		
I_n Equivalent input noise current		25°C		0.6			0.6		fA/ $\sqrt{\text{Hz}}$
Gain-bandwidth product	$f = 1\text{ kHz}, R_L = 50\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C		0.187			0.187		MHz
B_{OM} Maximum output-swing bandwidth	$V_{O(PP)} = 1\text{ V}, R_L = 50\text{ k}\Omega^\ddagger, A_V = 1, C_L = 100\text{ pF}^\ddagger$	25°C		60			60		kHz
ϕ_m Phase margin at unity gain	$R_L = 50\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C		63°			63°		
Gain margin	$R_L = 50\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C		15			15		dB

† Full range is -40°C to 125°C .

‡ Referenced to 1.5 V

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TLV2252 electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2252			TLV2252A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD\pm} = \pm 2.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C		200	1500		200	850	μV
		Full range			1750			1000	
α_{VIO} Temperature coefficient of input offset voltage	$V_{DD\pm} = \pm 2.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C to 85°C		0.5			0.5		$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)	$V_{DD\pm} = \pm 2.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C		0.003			0.003		$\mu\text{V}/\text{mo}$
I_{IO} Input offset current	$V_{DD\pm} = \pm 2.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C		0.5	60		0.5	60	pA
		125°C			1000			1000	
I_{IB} Input bias current	$V_{DD\pm} = \pm 2.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C		1	60		1	60	pA
		125°C			1000			1000	
V_{ICR} Common-mode input voltage range	$ V_{IO} \leq 5\text{ mV}$, $R_S = 50\ \Omega$	25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2		V
		Full range	0 to 3.5			0 to 3.5			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C		4.98			4.98		V
	$I_{OH} = -75\ \mu\text{A}$			4.9	4.94		4.9	4.94	
		Full range		4.8			4.8		
	$I_{OH} = -150\ \mu\text{A}$	25°C		4.8	4.88		4.8	4.88	
V_{OL} Low-level output voltage	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$	25°C		0.01			0.01		V
	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$			0.09	0.15		0.09	0.15	
		Full range			0.15			0.15	
	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C		0.2	0.3		0.2	0.3	
		Full range			0.3			0.3	
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 2.5\text{ V}$, $V_O = 1\text{ V to }4\text{ V}$	$R_L = 100\text{ k}\Omega^\ddagger$	25°C	100	350		100	350	V/mV
			Full range	10			10		
		$R_L = 1\text{ M}\Omega^\ddagger$	25°C		1700			1700	
$r_{i(d)}$ Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$ Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$c_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}$	25°C		8			8		pF
z_o Closed-loop output impedance	$f = 25\text{ kHz}$, $A_V = 10$	25°C		200			200		Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }2.7\text{ V}$, $V_O = 2.5\text{ V}$, $R_S = 50\ \Omega$	25°C		70	83		70	83	dB
		Full range		70			70		
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 4.4\text{ V to }8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C		80	95		80	95	dB
		Full range		80			80		

† Full range is -40°C to 125°C .

‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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TLV2252 electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2252			TLV2252A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current	$V_O = 2.5\text{ V}$, No load	25°C		70	125		70	125	μA
		Full range			150			150	

† Full range is -40°C to 125°C for Q level part.

TLV2252 operating characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2252			TLV2252A			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 1.25 V to 2.75 V, R _L = 100 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.07	0.12		0.07	0.12		V/μs
				Full range	0.05			0.05			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	36			36			nV/√Hz
		f = 1 kHz		25°C	19			19			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	0.7			0.7			μV
		f = 0.1 Hz to 10 Hz		25°C	1.1			1.1			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
THD+N	Total harmonic distortion plus noise	V _O = 0.5 V to 2.5 V, f = 20 kHz, R _L = 50 kΩ [‡]	A _V = 1	25°C	0.2%			0.2%			
			A _V = 10		1%			1%			
Gain-bandwidth product		f = 50 kHz, C _L = 100 pF [‡]	R _L = 50 kΩ [‡] ,	25°C	0.2			0.2			MHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 2 V, R _L = 50 kΩ [‡] ,	A _V = 1, C _L = 100 pF [‡]	25°C	30			30			kHz
φ _m	Phase margin at unity gain	R _L = 50 kΩ [‡] ,	C _L = 100 pF [‡]	25°C	63°			63°			
Gain margin		R _L = 50 kΩ [‡] ,	C _L = 100 pF [‡]	25°C	15			15			dB

† Full range is -40°C to 125°C .

‡ Referenced to 2.5 V



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TLV2254 electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2254			TLV2254A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} \pm \pm 1.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C		200	1500		200	850	μV
		Full range			1750			1000	
α_{VIO} Temperature coefficient of input offset voltage	$V_{DD} \pm \pm 1.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C to 125°C		0.5			0.5		$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)	$V_{DD} \pm \pm 1.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C		0.003			0.003		$\mu\text{V}/\text{mo}$
I_{IO} Input offset current	$V_{DD} \pm \pm 1.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C		0.5	60		0.5	60	pA
		125°C			1000			1000	
I_{IB} Input bias current	$V_{DD} \pm \pm 1.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	25°C		1	60		1	60	pA
		125°C			1000			1000	
V_{ICR} Common-mode input voltage range	$R_S = 50\ \Omega$, $ V_{IO} \leq 5\text{ mV}$	25°C	0 to 2	-0.3 to 2.2		0 to 2	-0.3 to 2.2		V
		Full range	0 to 1.7			0 to 1.7			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C			2.98			2.98	V
	$I_{OH} = -75\ \mu\text{A}$				2.9			2.9	
		Full range			2.8			2.8	
	$I_{OH} = -150\ \mu\text{A}$	25°C			2.8			2.8	
V_{OL} Low-level output voltage	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$	25°C			10			10	mV
	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$				100 150			100 150	
		Full range			165			165	
	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C			200 300			200 300	
		Full range			300			300	
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 1.5\text{ V}$, $V_O = 1\text{ V to }2\text{ V}$	25°C		100	225		100	225	V/mV
		Full range		10			10		
		25°C			800			800	
$r_{i(d)}$ Differential input resistance		25°C			10^{12}			10^{12}	Ω
$r_{i(c)}$ Common-mode input resistance		25°C			10^{12}			10^{12}	Ω
$c_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}$	25°C			8			8	pF
z_o Closed-loop output impedance	$f = 25\text{ kHz}$, $A_V = 10$	25°C			220			220	Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }1.7\text{ V}$, $V_O = 1.5\text{ V}$, $R_S = 50\ \Omega$	25°C		65	75		65	77	dB
		Full range		60			60		
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 2.7\text{ V to }8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C		80	95		80	100	dB
		Full range		80			80		

† Full range is -40°C to 125°C .

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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TLV2254 electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2254			TLV2254A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current (four amplifiers)	$V_O = 1.5\text{ V}$, No load	25°C		135	250		135	250	μA
		Full range			300			300	

† Full range is -40°C to 125°C for Q level part.

TLV2254 operating characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2254			TLV2254A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
SR Slew rate at unity gain	$V_O = 0.5\text{ V}$ to 1.7 V , $R_L = 100\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C	0.07	0.1		0.07	0.1		$\text{V}/\mu\text{s}$
		Full range	0.05			0.05			
V_n Equivalent input noise voltage	$f = 10\text{ Hz}$	25°C		35			35		$\text{nV}/\sqrt{\text{Hz}}$
	$f = 1\text{ kHz}$			19			19		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz}$ to 1 Hz	25°C		0.6			0.6		μV
	$f = 0.1\text{ Hz}$ to 10 Hz			1.1			1.1		
I_n Equivalent input noise current		25°C		0.6			0.6		$\text{fA}/\sqrt{\text{Hz}}$
Gain-bandwidth product	$f = 1\text{ kHz}$, $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		0.187			0.187		MHz
B_{OM} Maximum output-swing bandwidth	$V_{O(PP)} = 1\text{ V}$, $A_V = 1$, $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		60			60		kHz
ϕ_m Phase margin at unity gain	$R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		63°			63°		
Gain margin	$R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		15			15		dB

† Full range is -40°C to 125°C for Q level part.

‡ Referenced to 1.5 V

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TLV2254 electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2254			TLV2254A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} = \pm 2.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C	200	1500		200	850		μV
		Full range		1750			1000		
α_{VIO} Temperature coefficient of input offset voltage	$V_{DD} = \pm 2.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C to 125°C	0.5			0.5			$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)	$V_{DD} = \pm 2.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C	0.003			0.003			$\mu\text{V}/\text{mo}$
I_{IO} Input offset current	$V_{DD} = \pm 2.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C	0.5	60		0.5	60		pA
		125°C		1000			1000		
I_{IB} Input bias current	$V_{DD} = \pm 2.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C	1	60		1	60		pA
		125°C		1000			1000		
V_{ICR} Common-mode input voltage range	$ V_{IO} \leq 5\text{ mV}$, $R_S = 50\ \Omega$	25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2		V
		Full range	0 to 3.5			0 to 3.5			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C	4.98			4.98			V
	$I_{OH} = -75\ \mu\text{A}$	25°C	4.9	4.94		4.9	4.94		
	$I_{OH} = -150\ \mu\text{A}$	25°C	4.8	4.88		4.8	4.88		
V_{OL} Low-level output voltage	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$	25°C	0.01			0.01			V
	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$	25°C	0.09	0.15		0.09	0.15		
		Full range		0.15			0.15		
	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C	0.2	0.3		0.2	0.3		
		Full range		0.3			0.3		
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 2.5\text{ V}$, $V_O = 1\text{ V to }4\text{ V}$	25°C	100	350		100	350		V/mV
	$R_L = 100\text{ k}\Omega^\ddagger$	Full range	10			10			
	$R_L = 1\text{ M}\Omega^\ddagger$	25°C	1700			1700			
$r_{i(d)}$ Differential input resistance		25°C	10^{12}			10^{12}			Ω
$r_{i(c)}$ Common-mode input resistance		25°C	10^{12}			10^{12}			Ω
$c_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}$	25°C	8			8			pF
z_o Closed-loop output impedance	$f = 25\text{ kHz}$, $A_V = 10$	25°C	200			200			Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }2.7\text{ V}$, $V_O = 2.5\text{ V}$, $R_S = 50\ \Omega$	25°C	70	83		70	83		dB
		Full range	70			70			
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 4.4\text{ V to }8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C	80	95		80	95		dB
		Full range	80			80			

† Full range is -40°C to 125°C .

‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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TLV2254 electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2254			TLV2254A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current (four amplifiers)	$V_O = 2.5\text{ V}$, No load	25°C		140	250		140	250	μA
		Full range			300			300	

† Full range is -40°C to 125°C .

TLV2254 operating characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2254			TLV2254A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
SR Slew rate at unity gain	$V_O = 0.5\text{ V}$ to 3.5 V , $R_L = 100\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C	0.07	0.12		0.07	0.12		$\text{V}/\mu\text{s}$
		Full range	0.05			0.05			
V_n Equivalent input noise voltage	$f = 10\text{ Hz}$ $f = 1\text{ kHz}$	25°C		36			36		$\text{nV}/\sqrt{\text{Hz}}$
				19			19		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz}$ to 1 Hz $f = 0.1\text{ Hz}$ to 10 Hz	25°C		0.7			0.7		μV
				1.1			1.1		
I_n Equivalent input noise current		25°C		0.6			0.6		$\text{fA}/\sqrt{\text{Hz}}$
THD+N Total harmonic distortion plus noise	$V_O = 0.5\text{ V}$ to 2.5 V , $f = 20\text{ kHz}$, $R_L = 50\text{ k}\Omega^\ddagger$	25°C		0.2%			0.2%		
				1%			1%		
Gain-bandwidth product	$f = 50\text{ kHz}$, $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		0.2			0.2		MHz
B_{OM} Maximum output-swinging bandwidth	$V_{O(PP)} = 2\text{ V}$, $R_L = 50\text{ k}\Omega^\ddagger$, $A_V = 1$, $C_L = 100\text{ pF}^\ddagger$	25°C		30			30		kHz
ϕ_m Phase margin at unity gain	$R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		63°			63°		
Gain margin	$R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		15			15		dB

† Full range is -40°C to 125°C for Q level part.

‡ Referenced to 2.5 V

TYPICAL CHARACTERISTICS

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TYPICAL CHARACTERISTICS

**DISTRIBUTION OF TLV2252
INPUT OFFSET VOLTAGE**

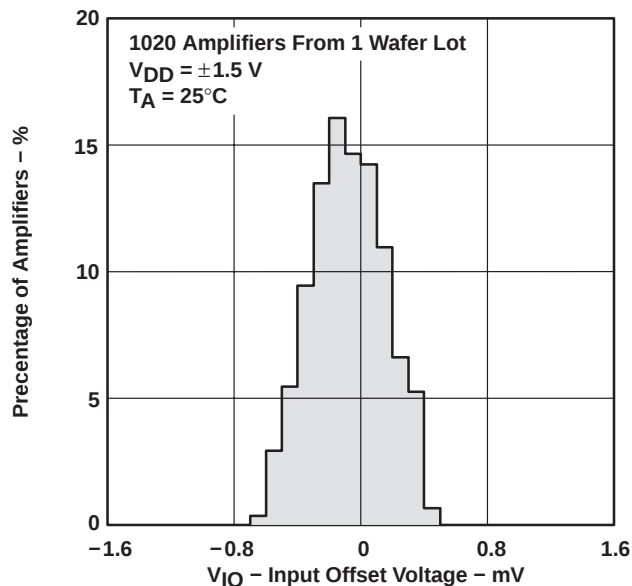


Figure 2

**DISTRIBUTION OF TLV2252
INPUT OFFSET VOLTAGE**

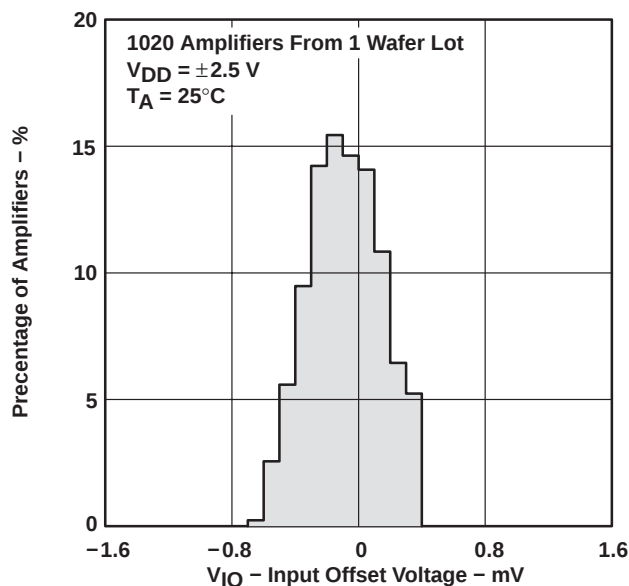


Figure 3

**DISTRIBUTION OF TLV2254
INPUT OFFSET VOLTAGE**

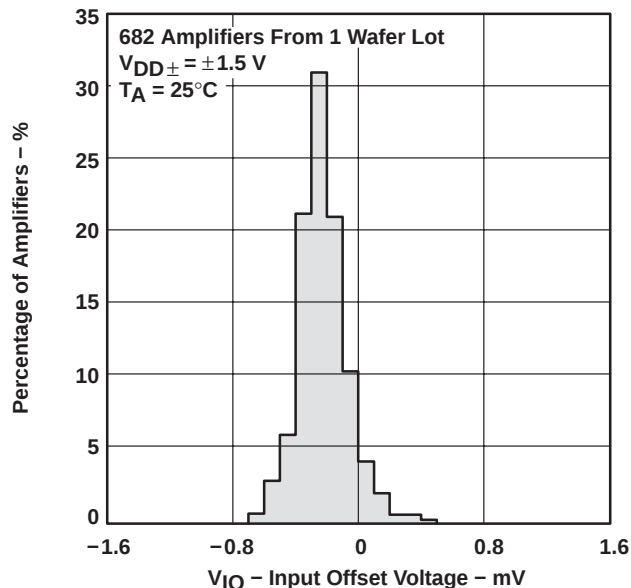


Figure 4

**DISTRIBUTION OF TLV2254
INPUT OFFSET VOLTAGE**

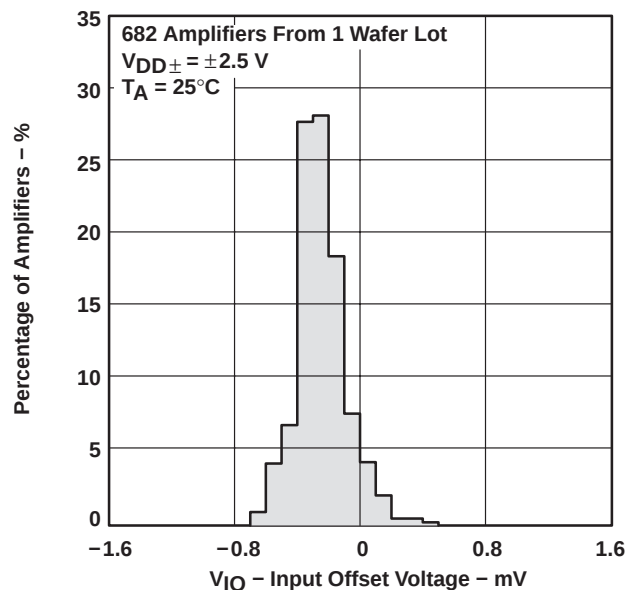


Figure 5

TYPICAL CHARACTERISTICS

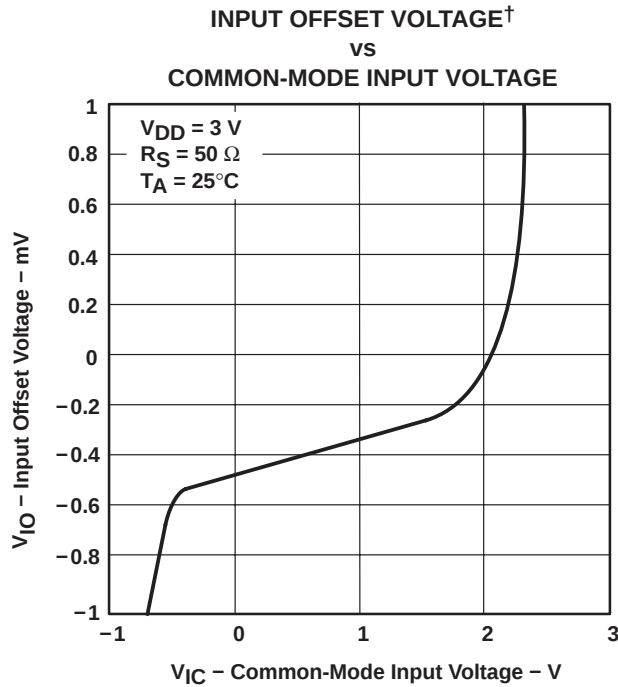


Figure 6

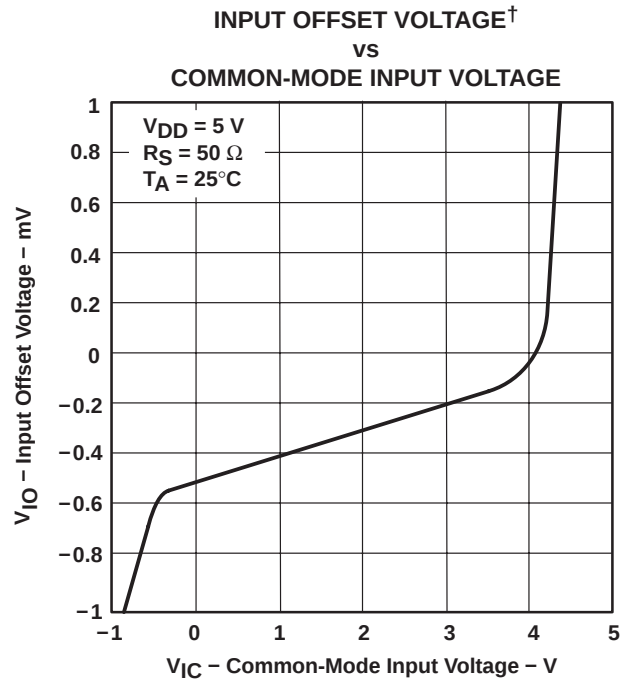


Figure 7

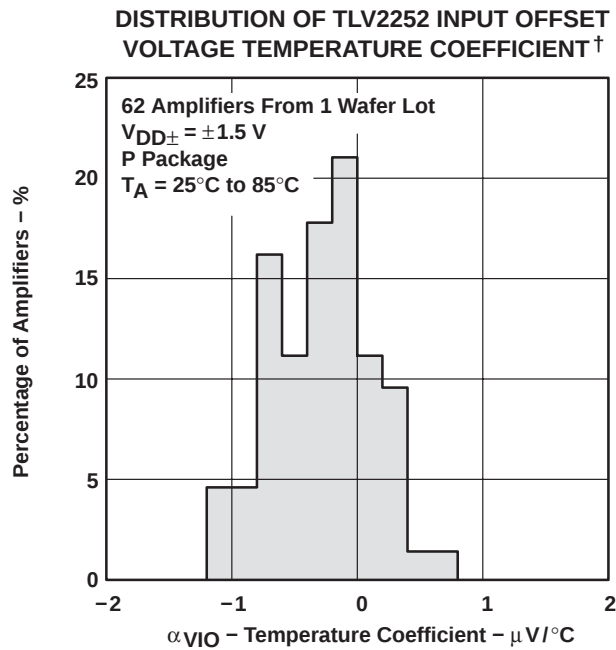


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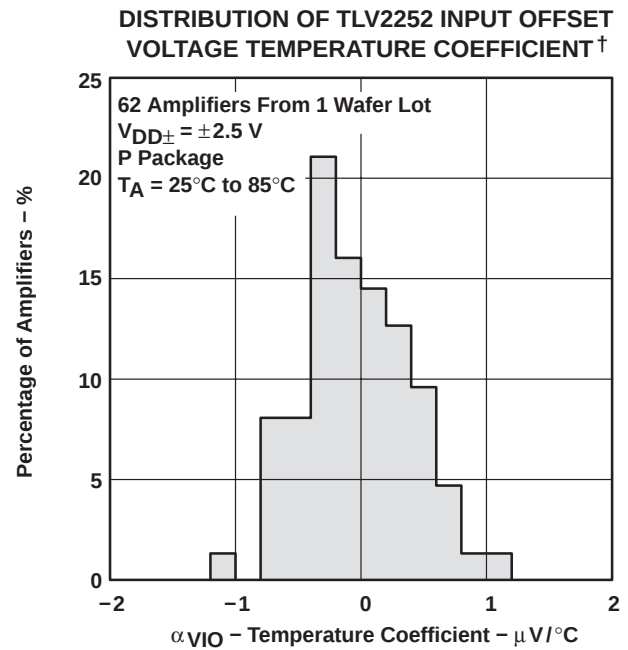


Figure 9

[†] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

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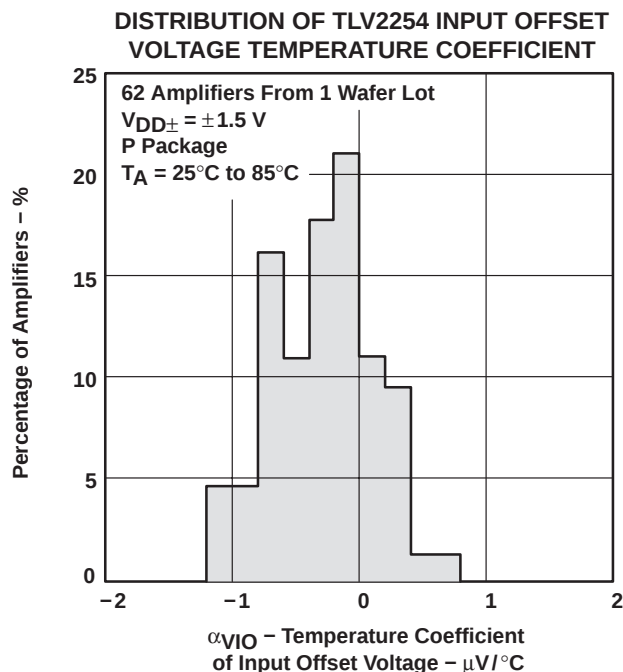


Figure 10

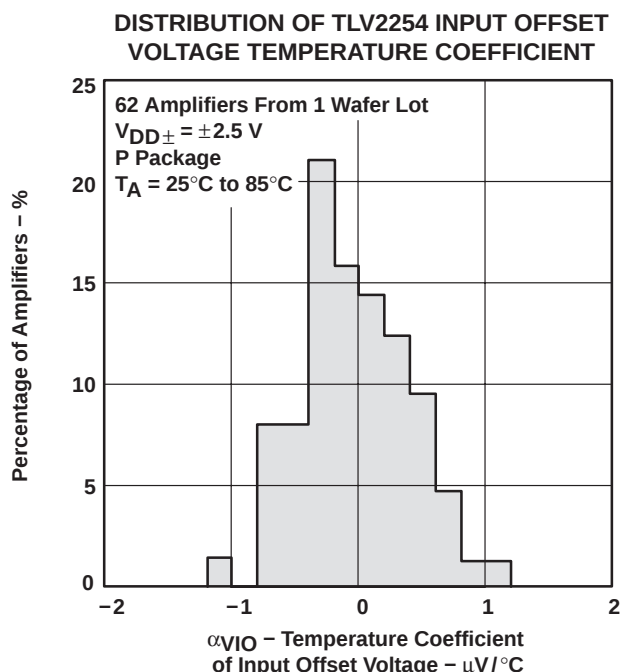


Figure 11

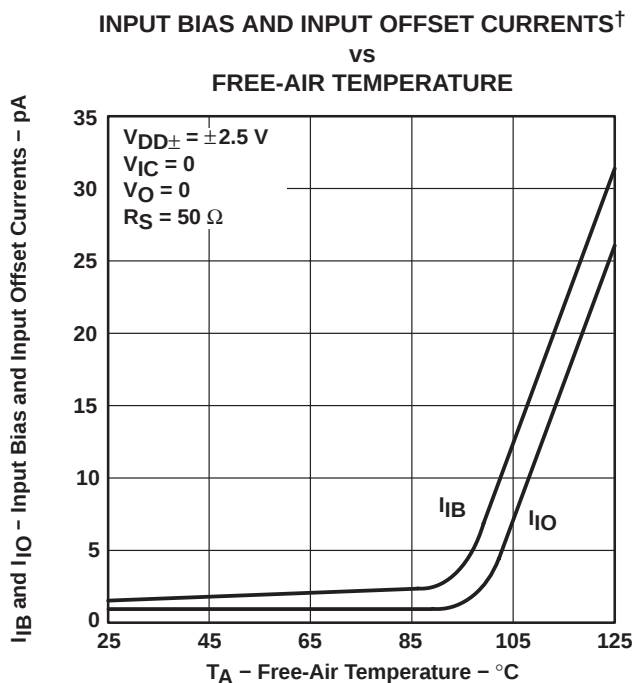


Figure 12

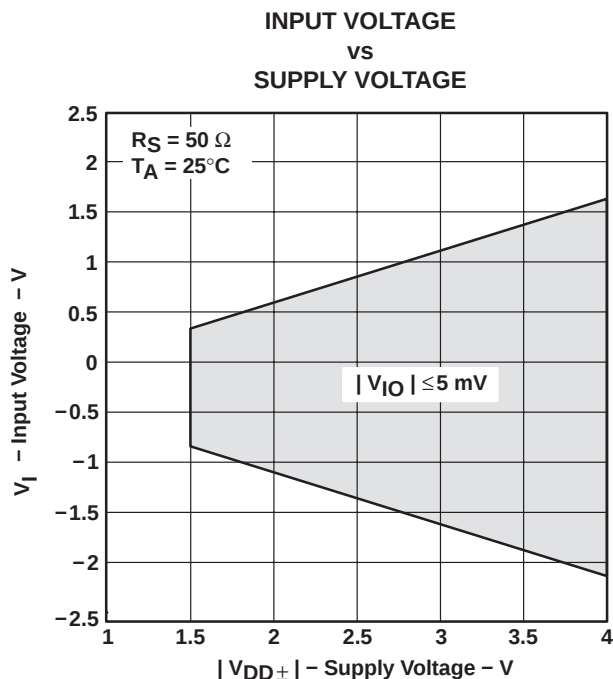
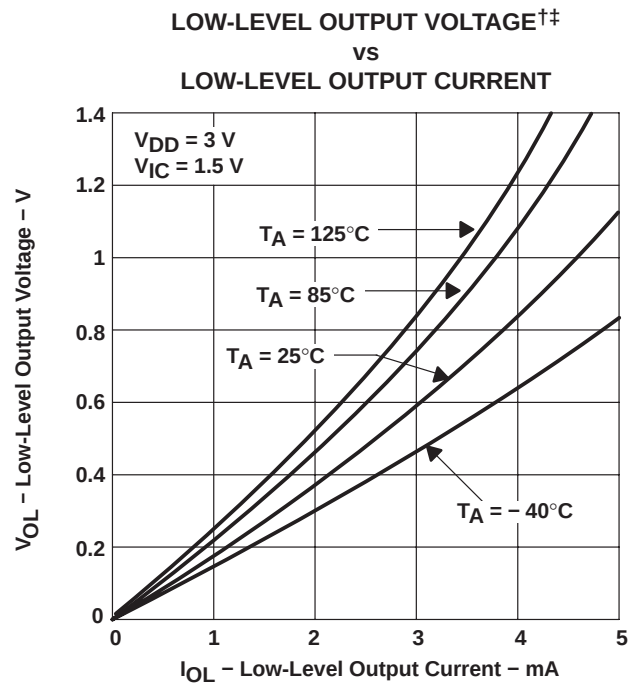
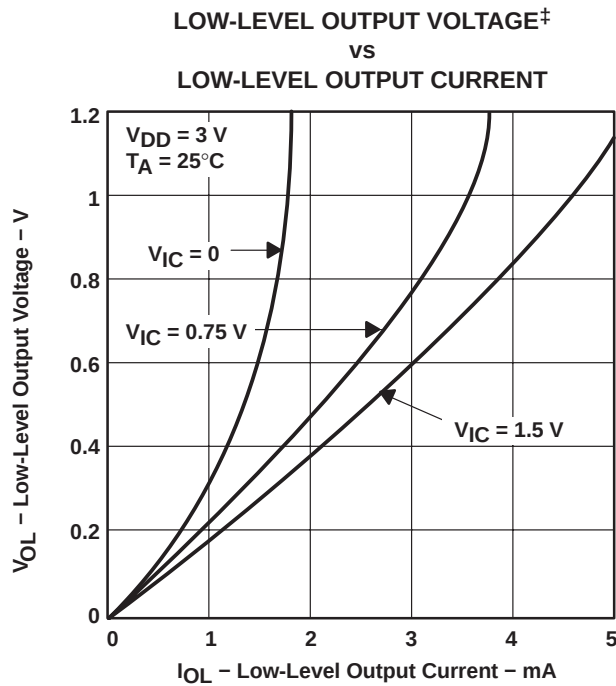
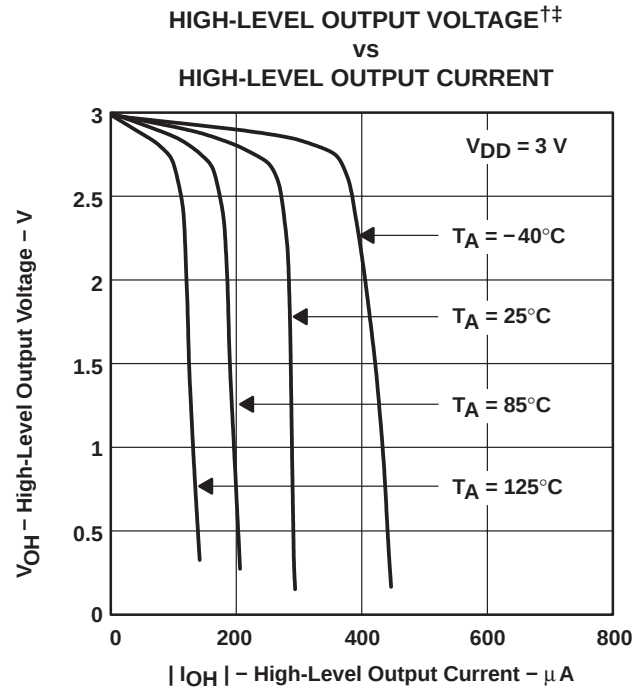
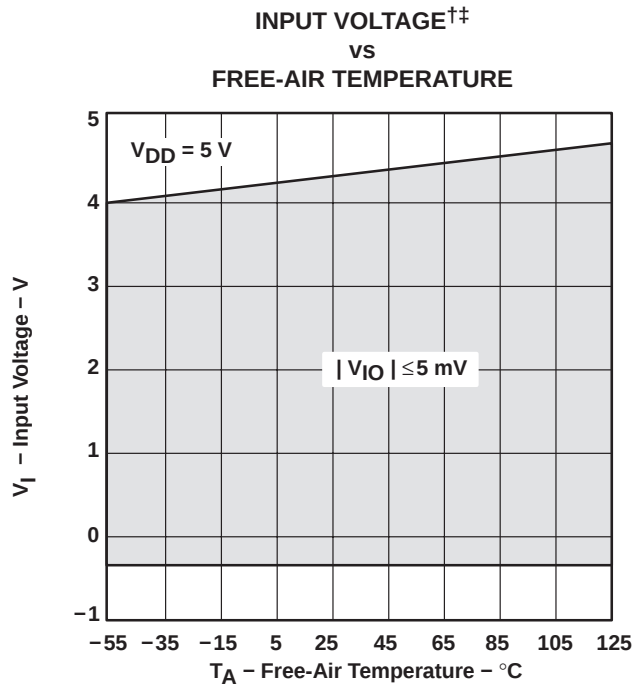


Figure 13

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5$ V, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3$ V, all loads are referenced to 1.5 V.

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TYPICAL CHARACTERISTICS

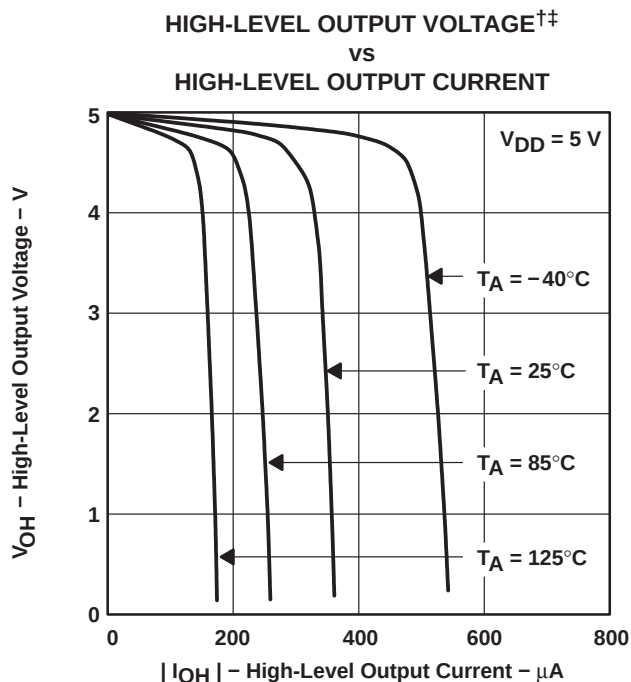


Figure 18

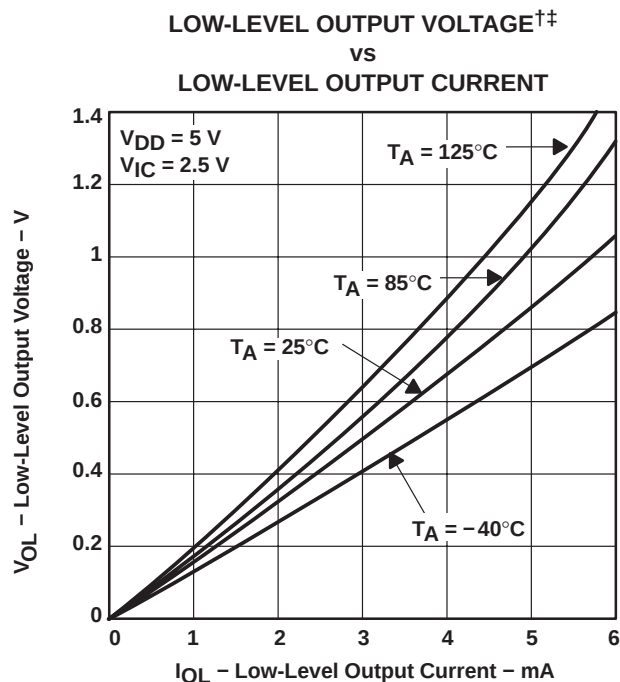


Figure 19

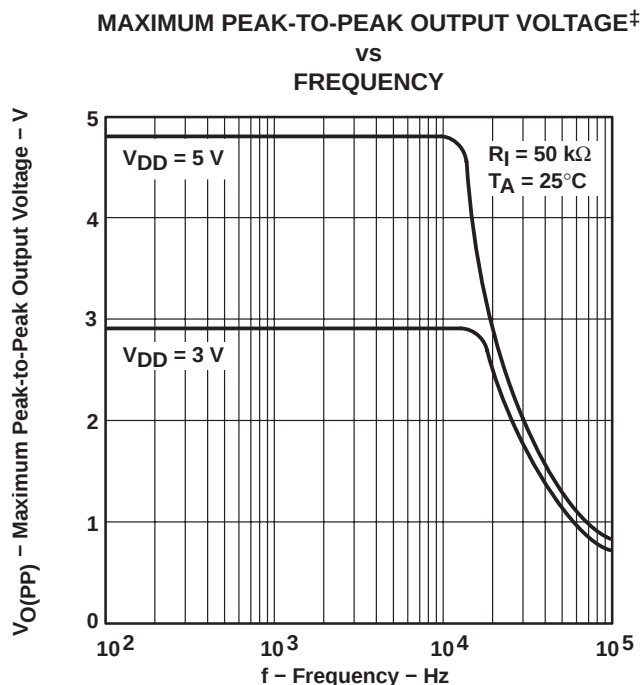


Figure 20

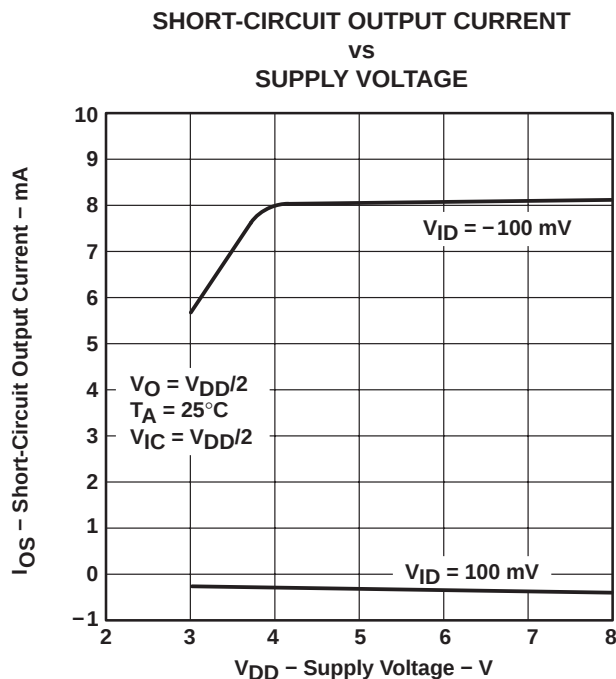
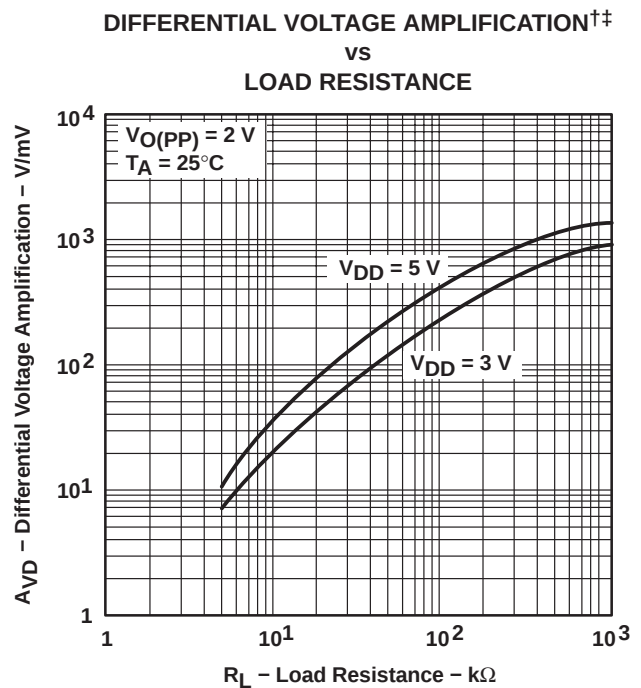
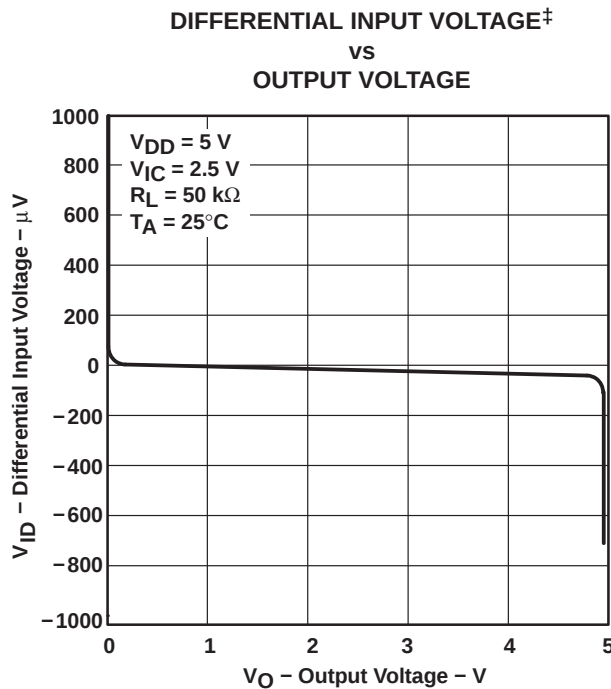
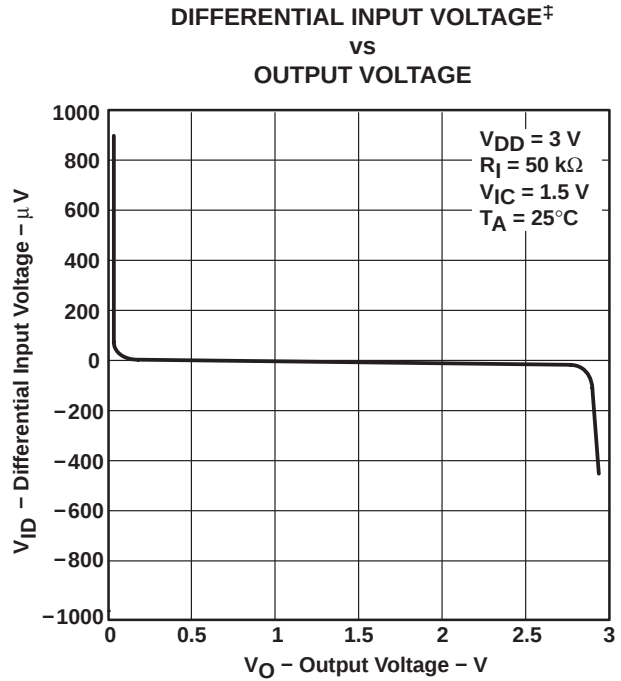
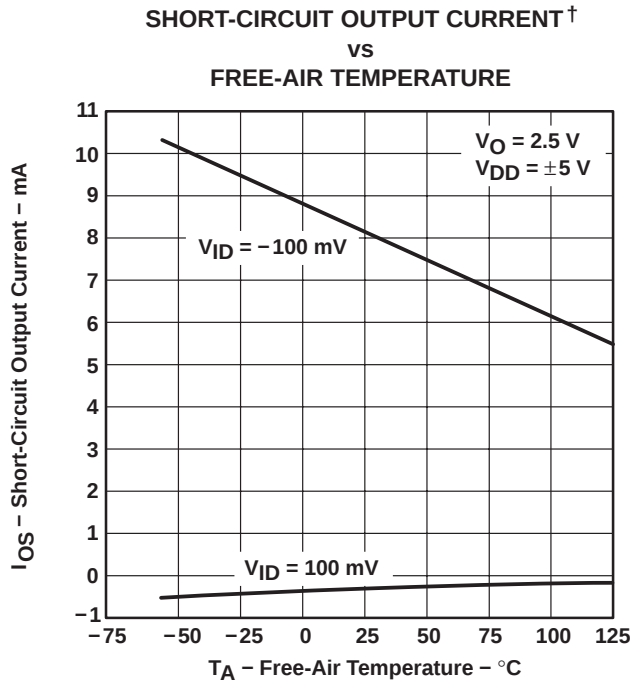


Figure 21

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where $V_{DD} = 5$ V, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3$ V, all loads are referenced to 1.5 V.

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TYPICAL CHARACTERISTICS

**LARGE-SIGNAL DIFFERENTIAL VOLTAGE†
AMPLIFICATION AND PHASE MARGIN**

**VS
FREQUENCY**

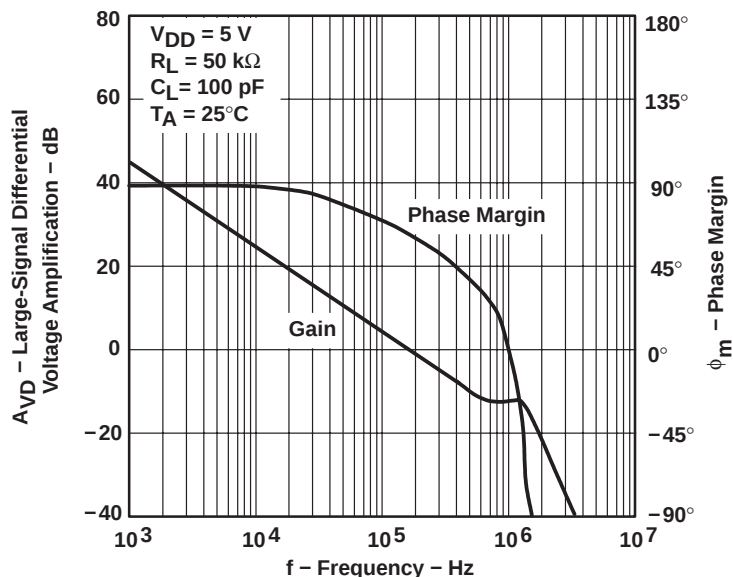


Figure 26

**LARGE-SIGNAL DIFFERENTIAL VOLTAGE†
AMPLIFICATION AND PHASE MARGIN**

**VS
FREQUENCY**

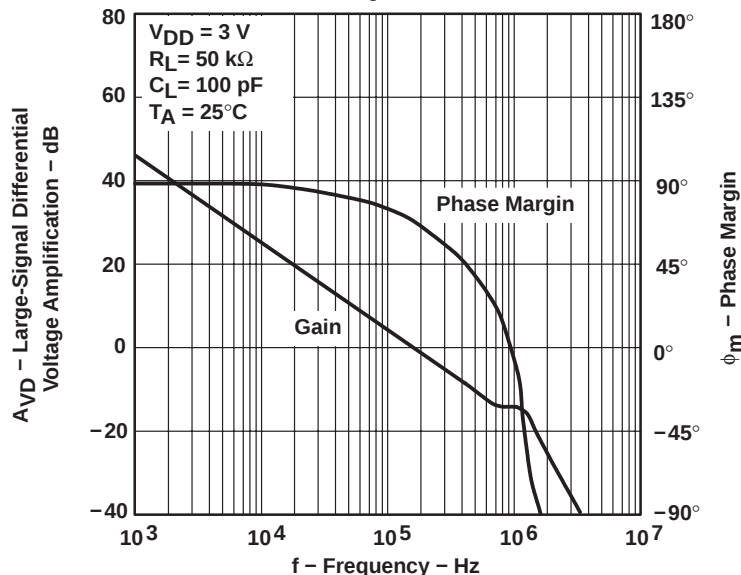


Figure 27

† For all curves where $V_{DD} = 5$ V, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3$ V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

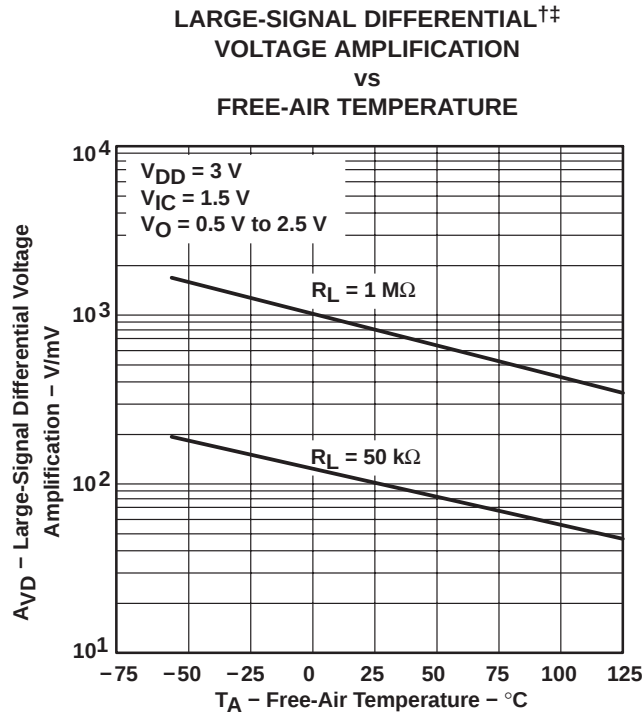


Figure 28

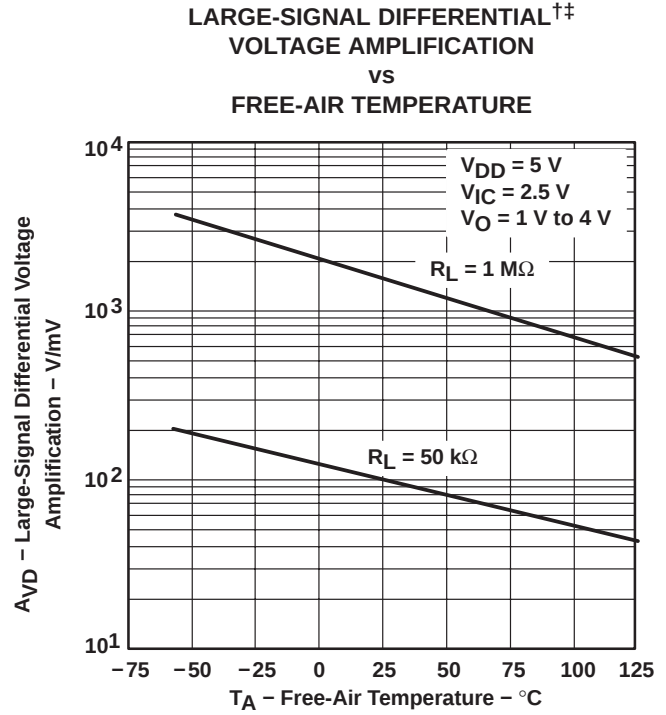


Figure 29

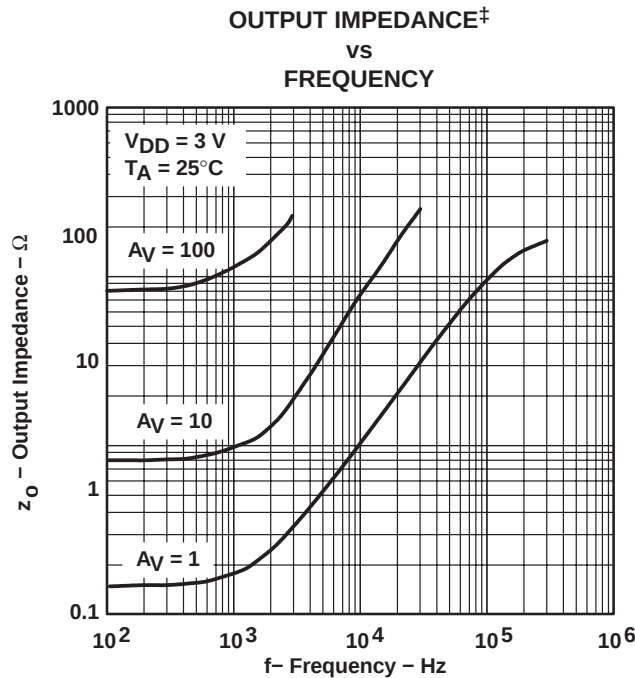


Figure 30

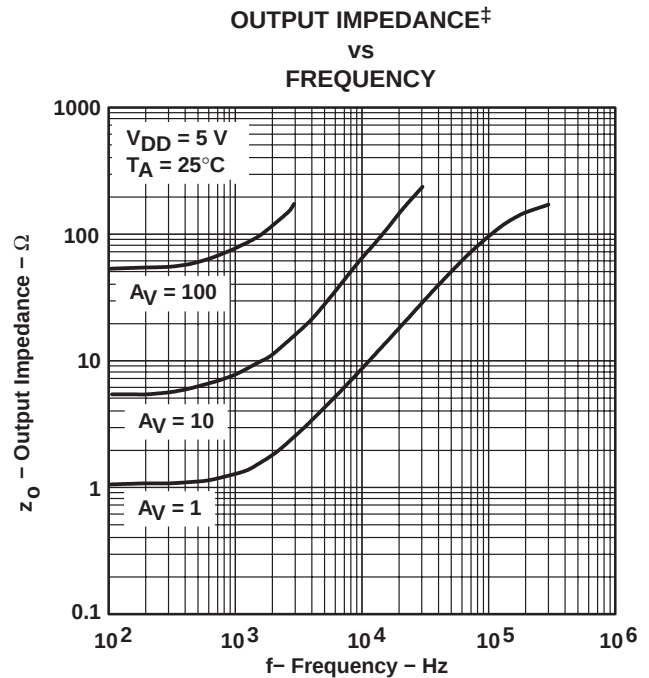


Figure 31

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

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TYPICAL CHARACTERISTICS

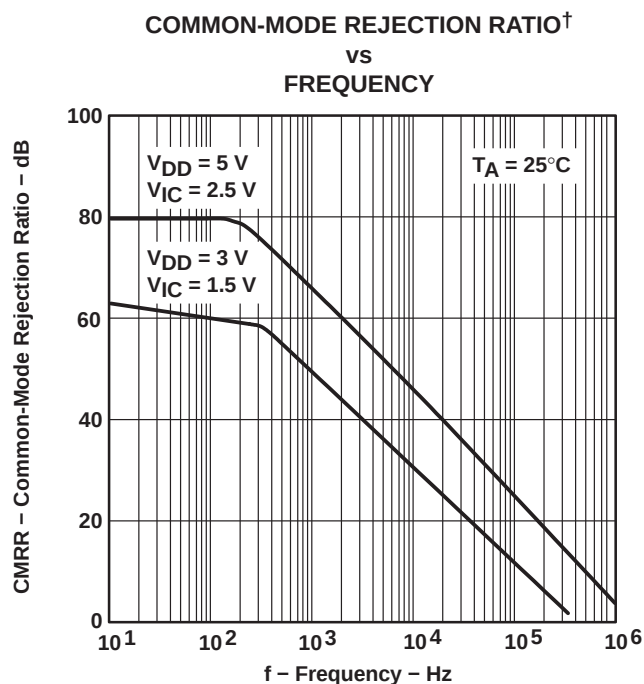


Figure 32

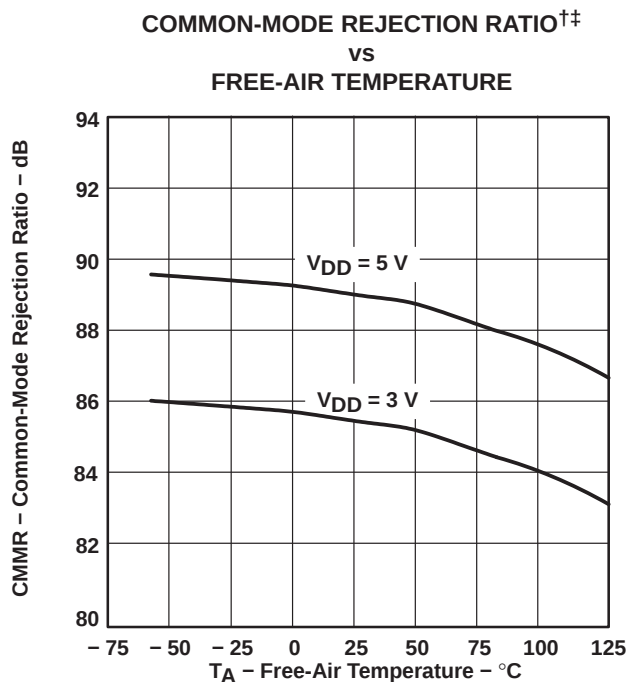


Figure 33

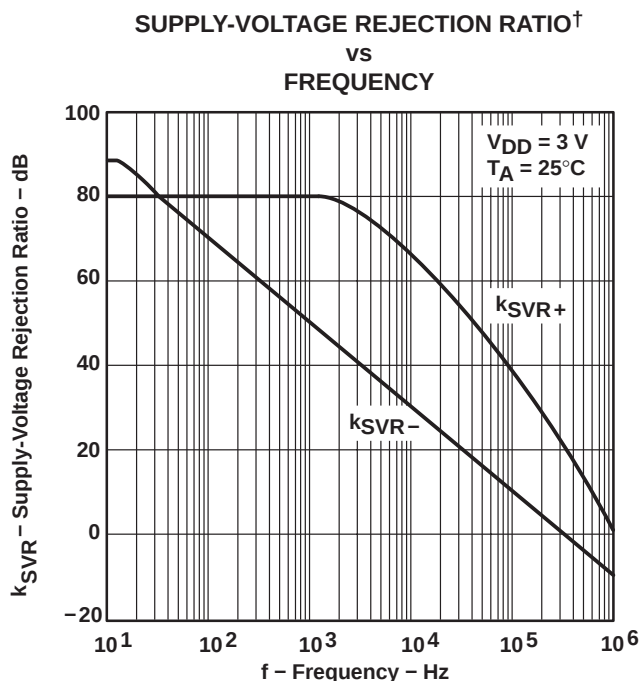


Figure 34

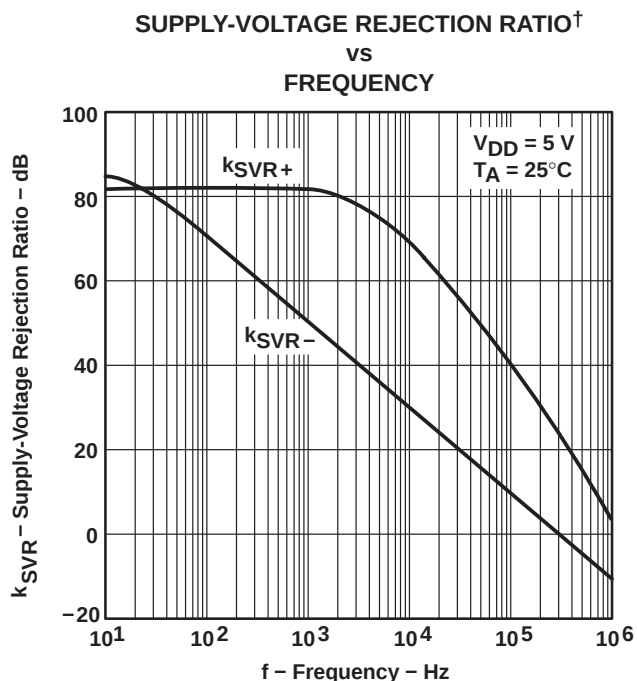


Figure 35

[†] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

[‡] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

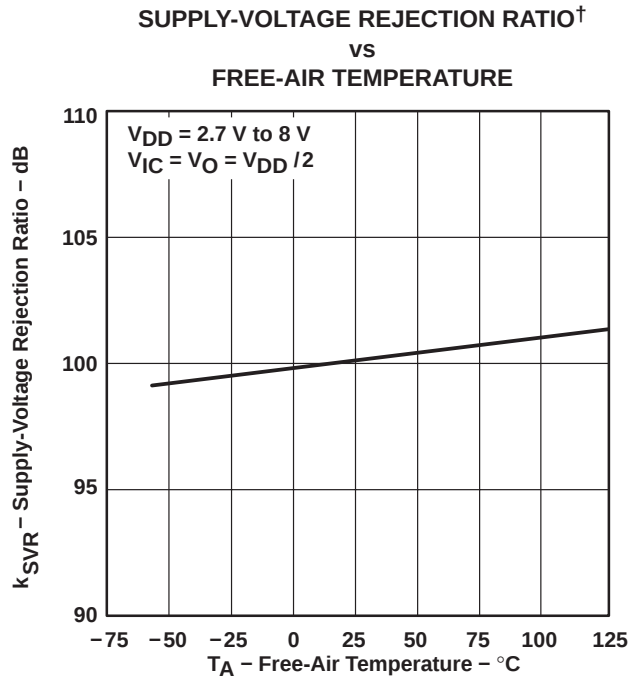


Figure 36

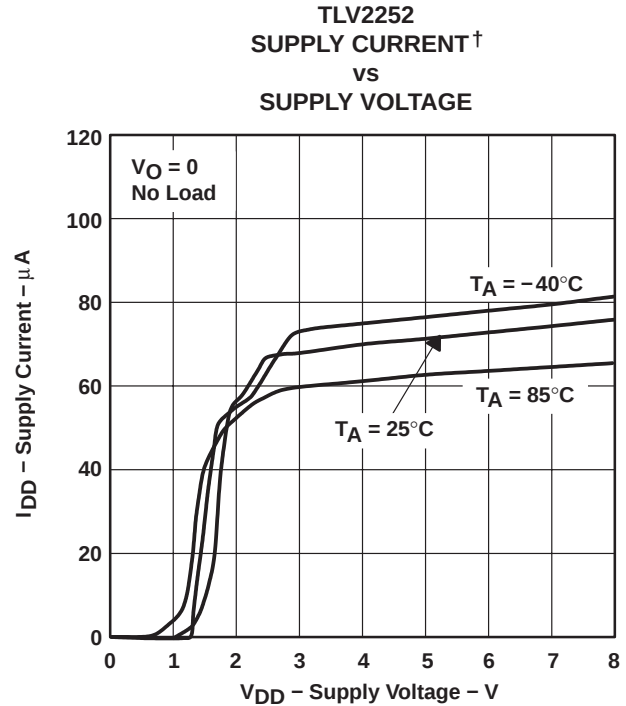


Figure 37

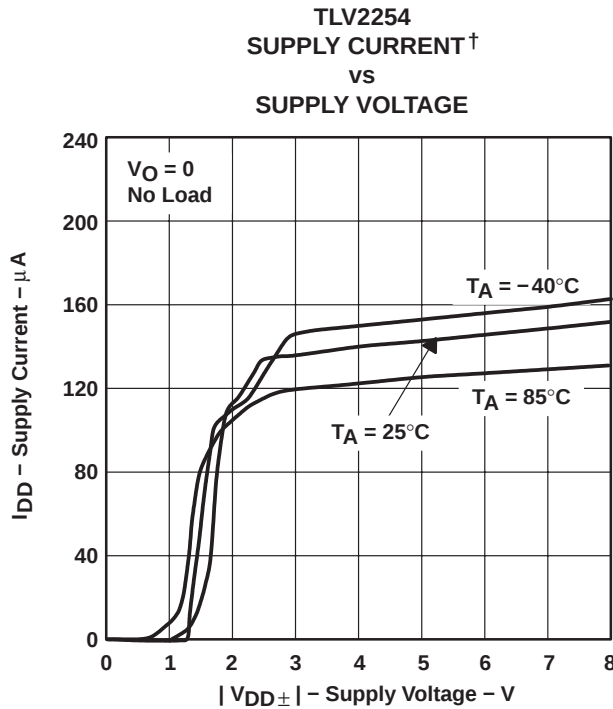


Figure 38

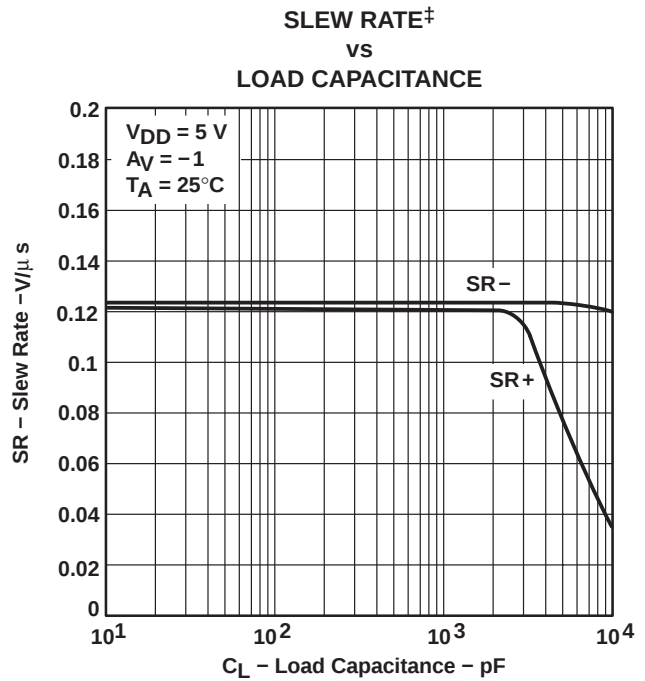


Figure 39

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where $V_{DD} = 5 \text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 \text{ V}$, all loads are referenced to 1.5 V.

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TYPICAL CHARACTERISTICS

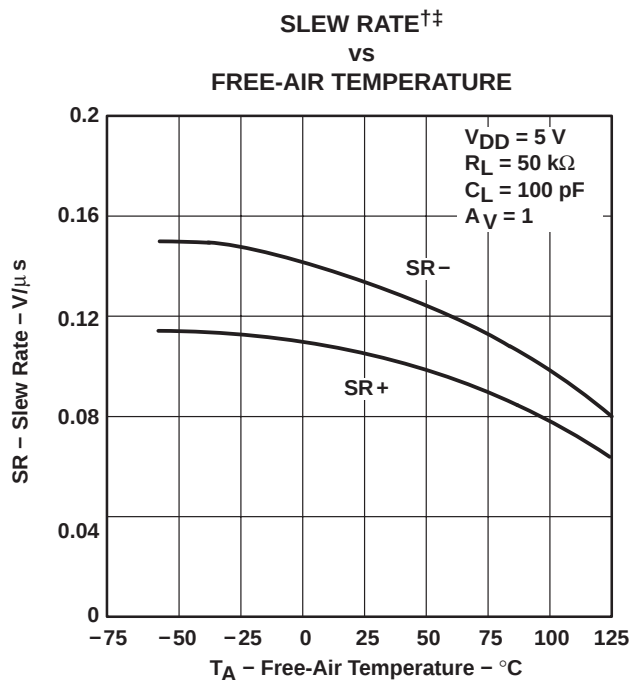


Figure 40

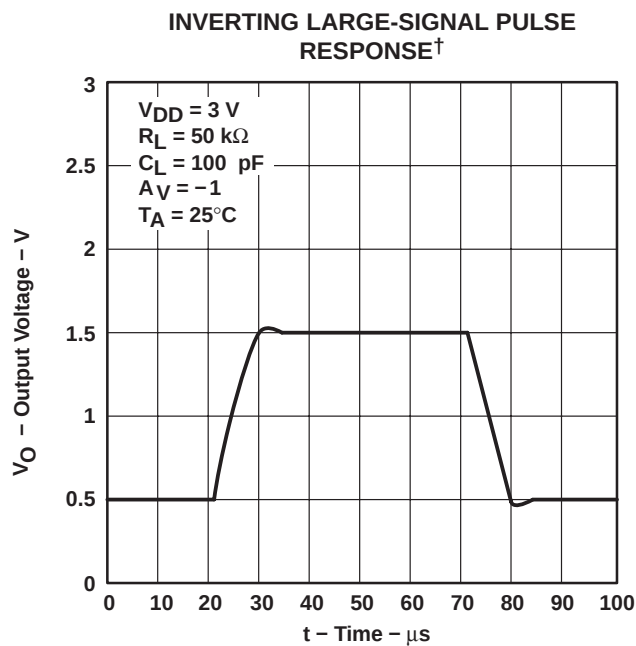


Figure 41

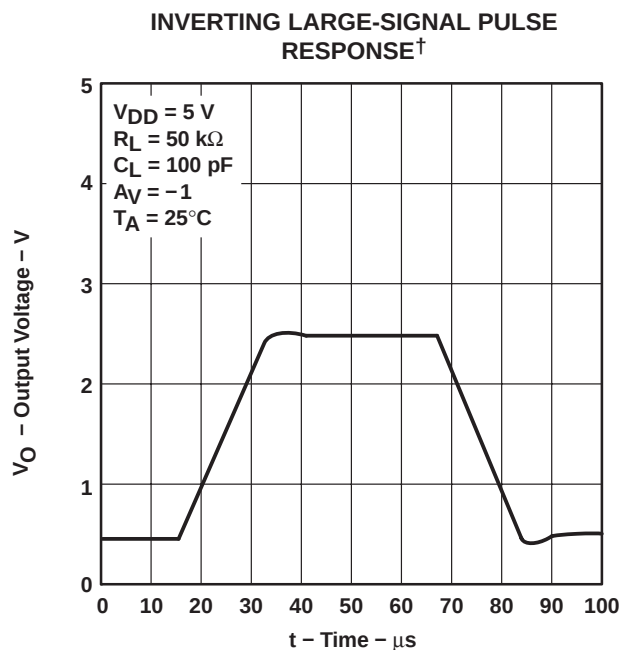


Figure 42

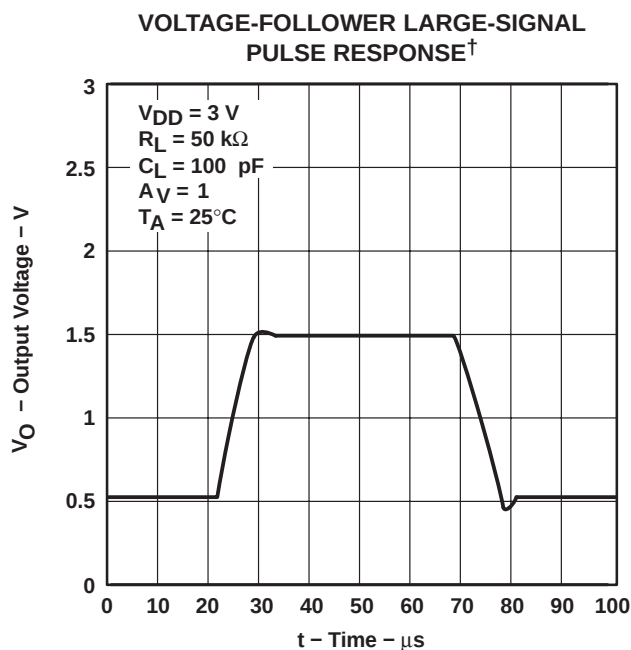


Figure 43

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

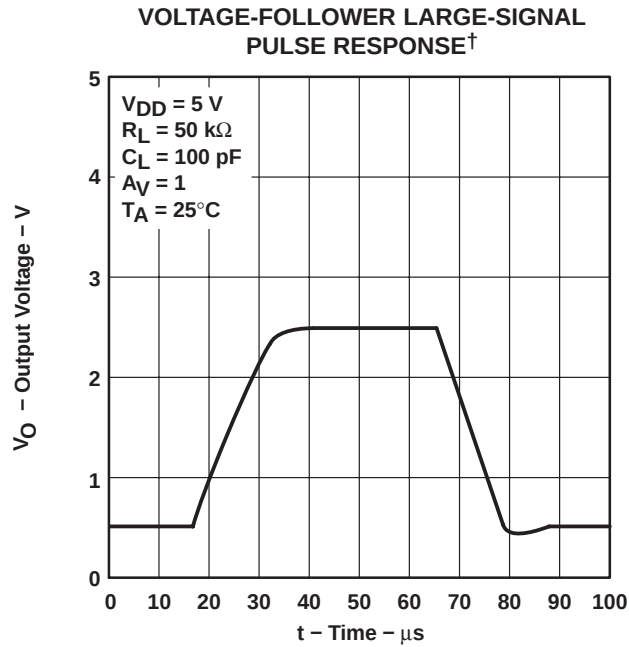


Figure 44

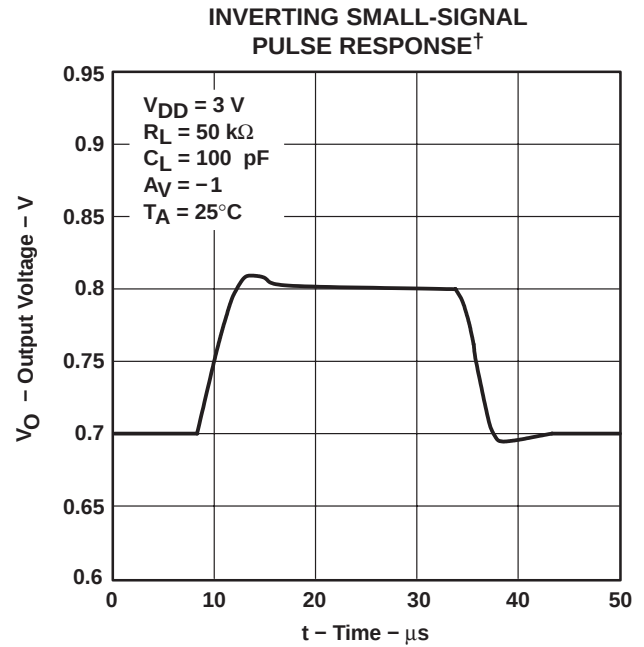


Figure 45

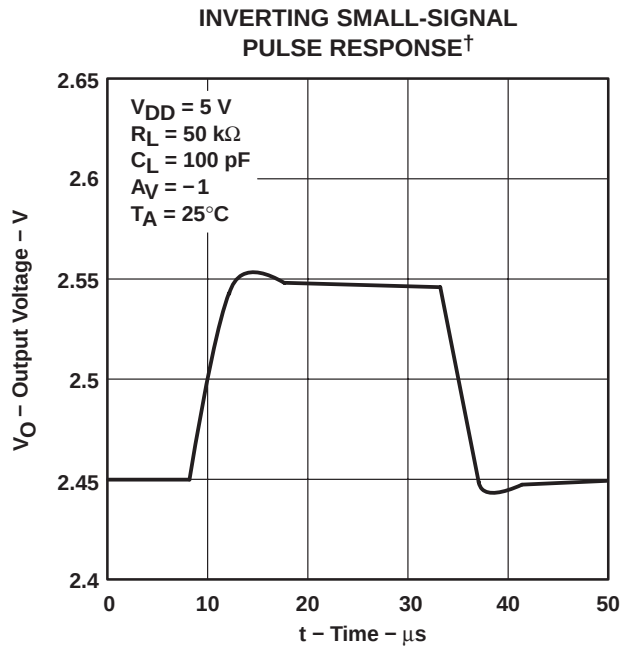


Figure 46

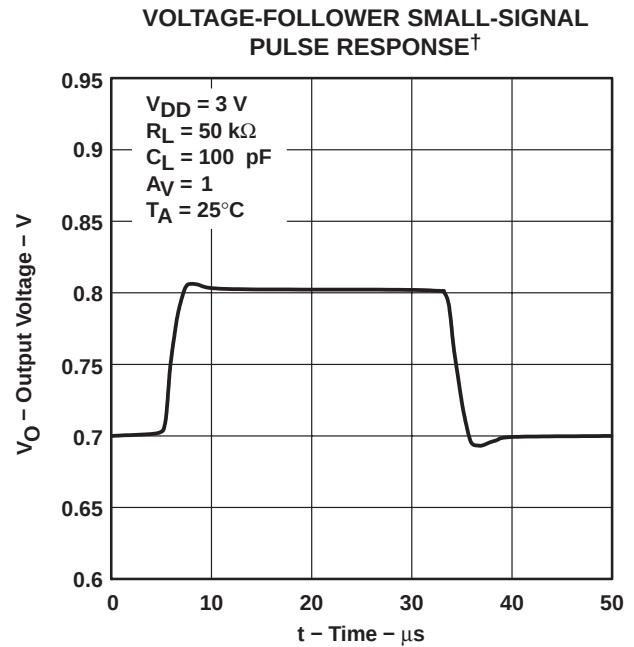


Figure 47

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

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TYPICAL CHARACTERISTICS

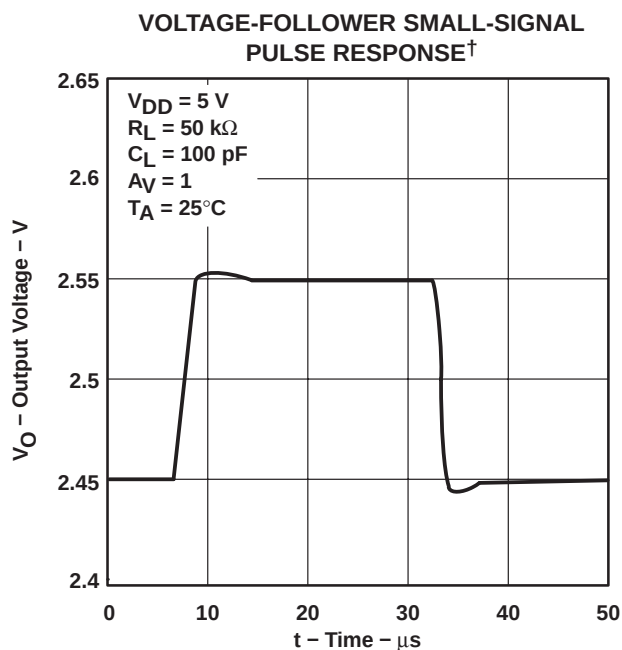


Figure 48

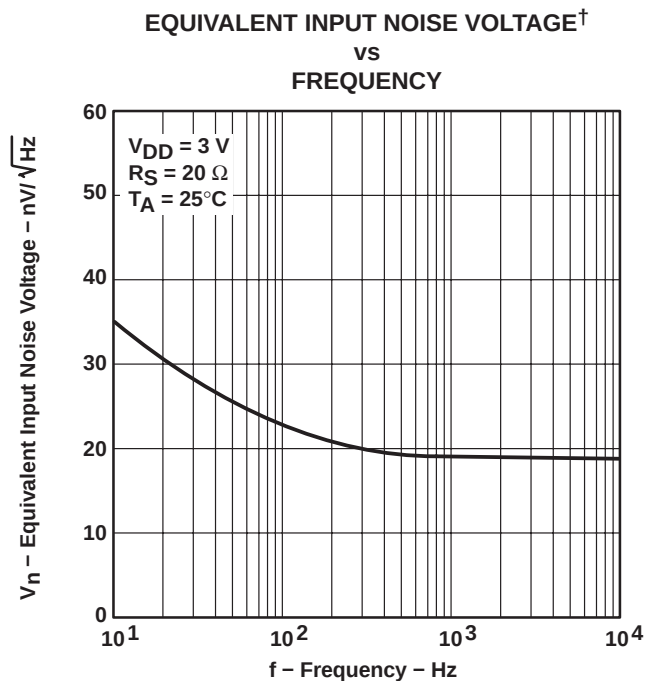


Figure 49

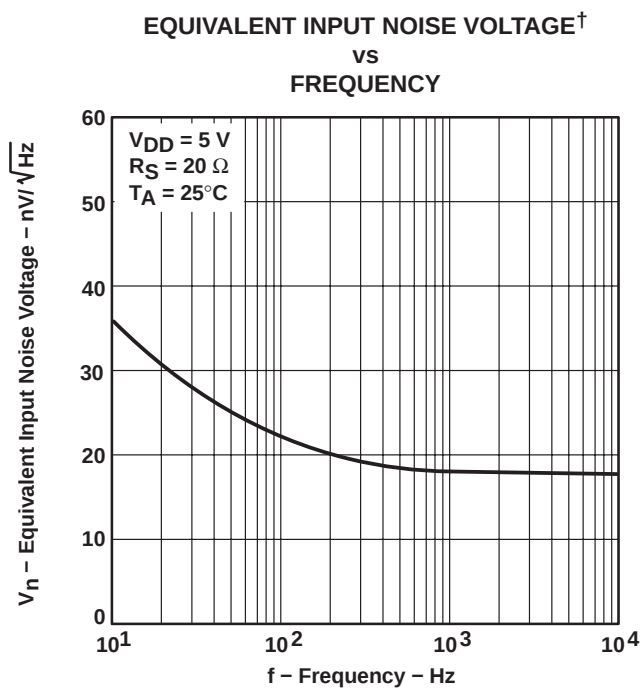


Figure 50

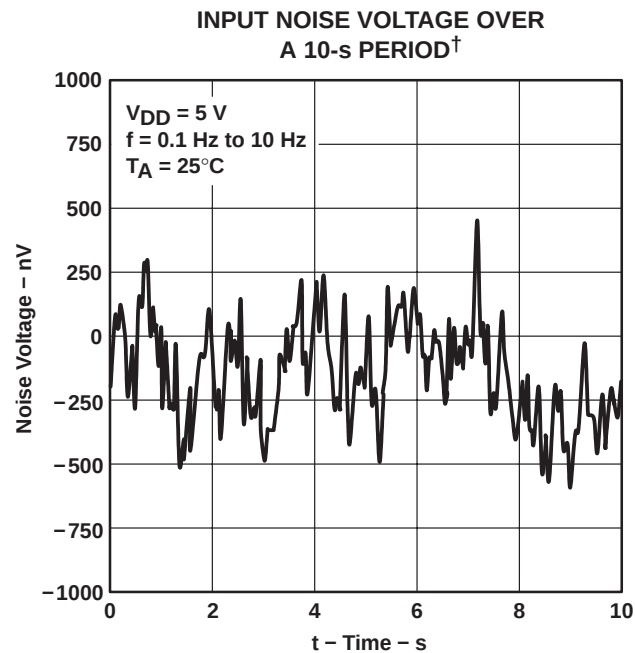


Figure 51

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

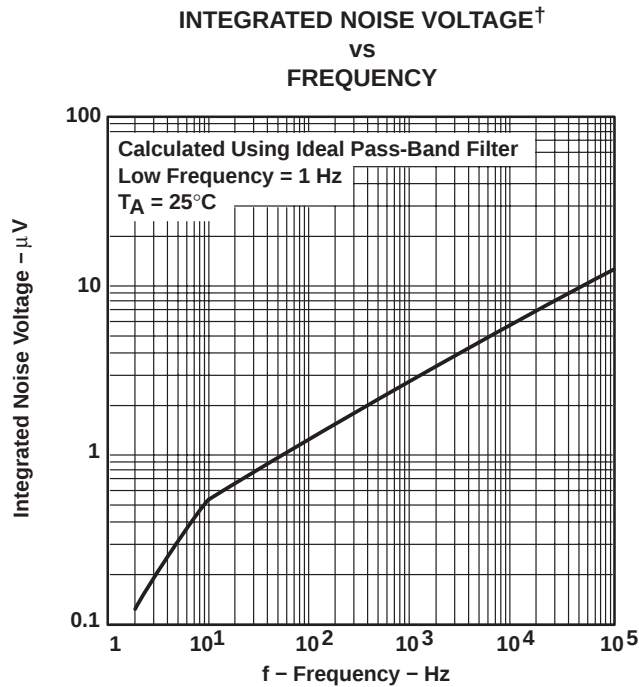


Figure 52

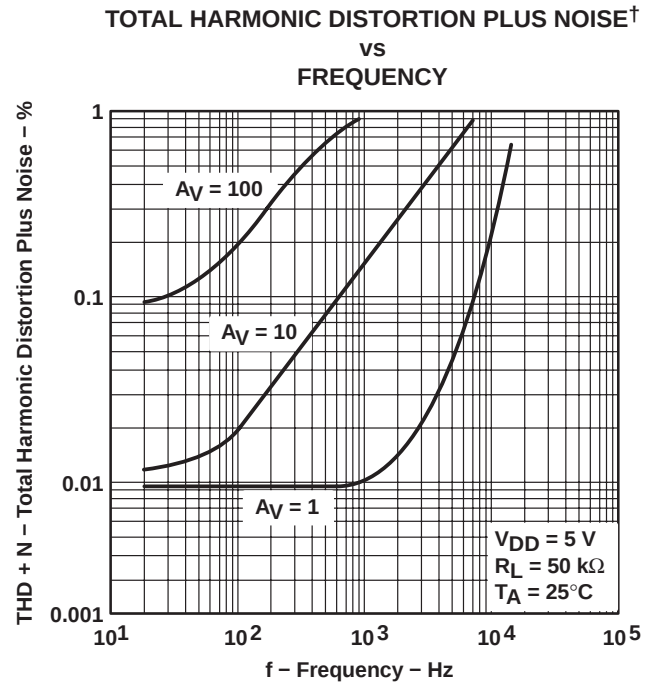


Figure 53

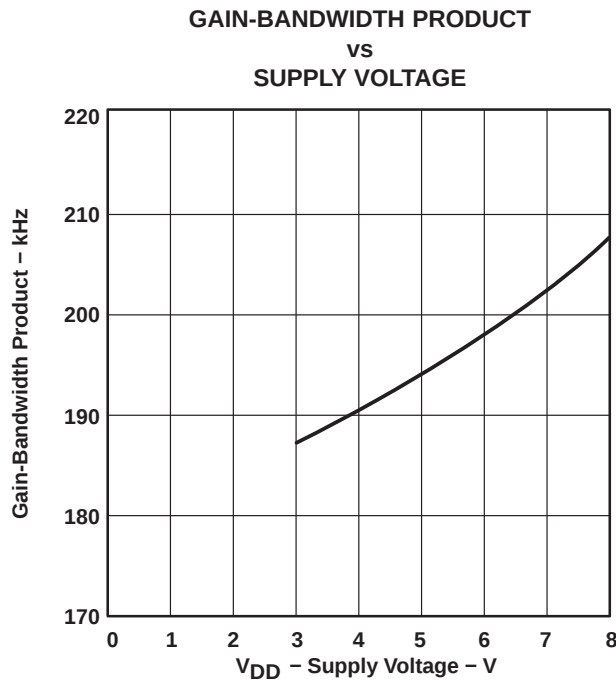


Figure 54

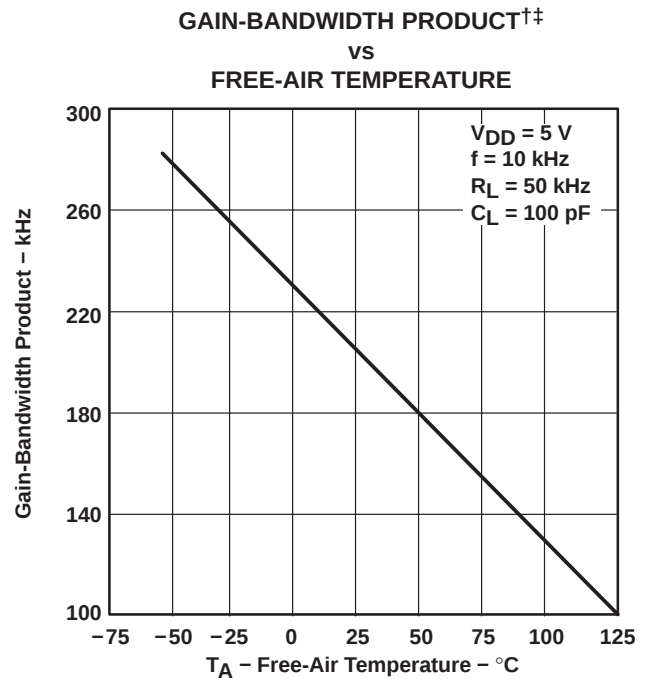


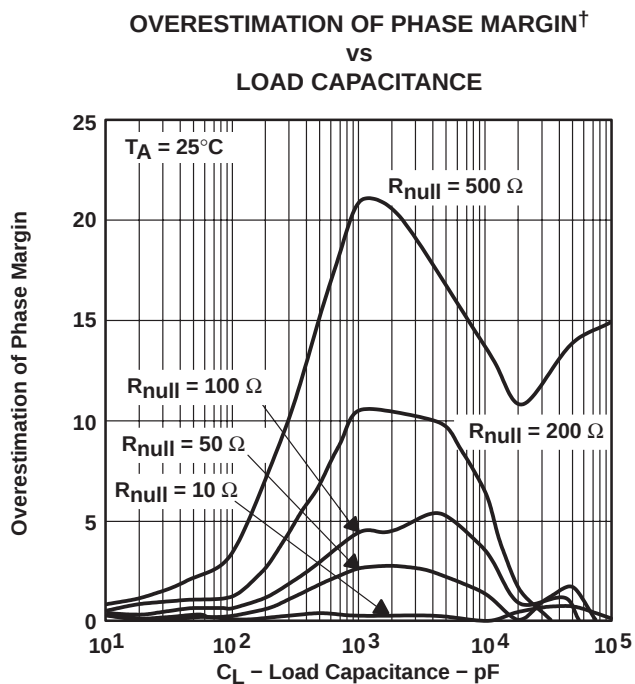
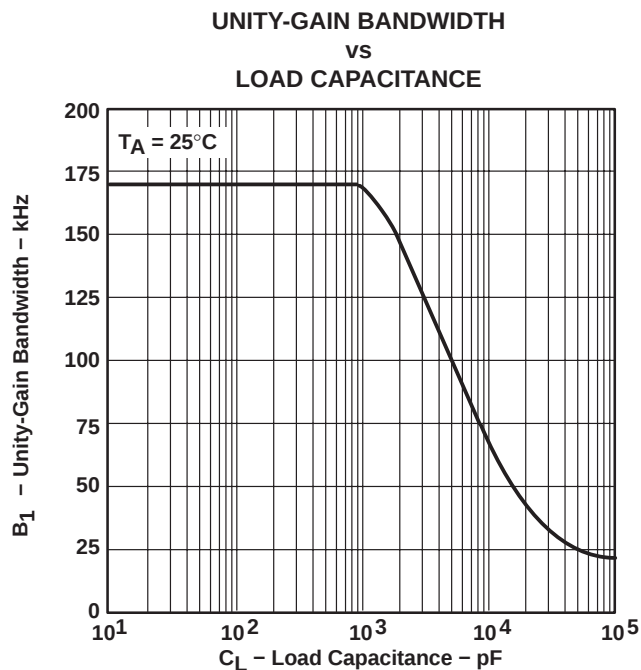
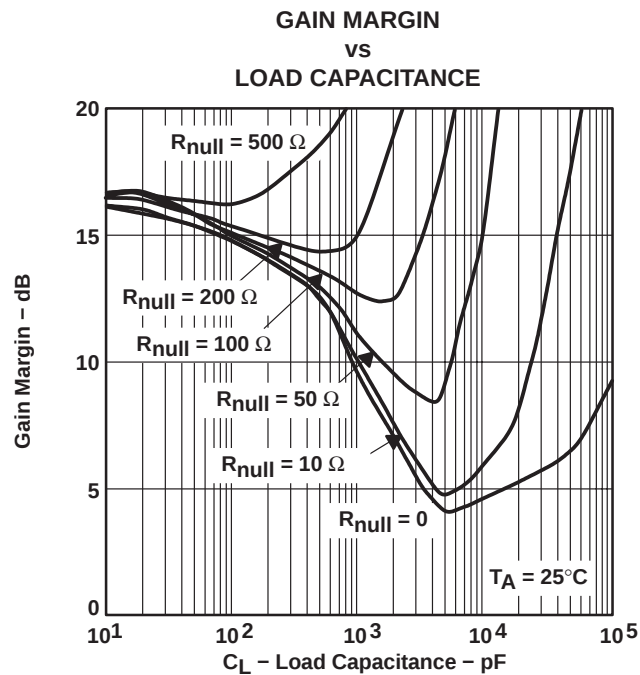
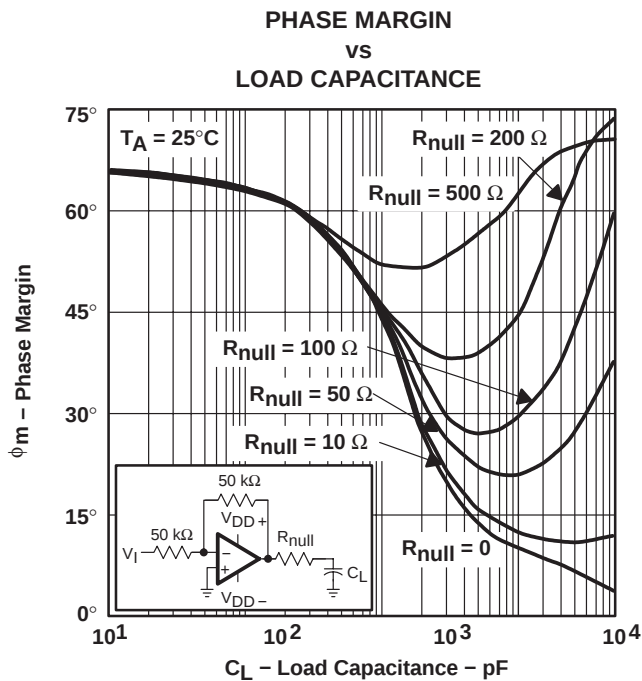
Figure 55

[†] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

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TYPICAL CHARACTERISTICS



† See application information

† For all curves where $V_{DD} = 5$ V, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3$ V, all loads are referenced to 1.5 V.

‡ Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

APPLICATION INFORMATION

driving large capacitive loads

The TLV2252 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 56 and Figure 57 illustrate its ability to drive loads up to 1000 pF while maintaining good gain and phase margins ($R_{null} = 0$).

A smaller series resistor (R_{null}) at the output of the device (see Figure 60) improves the gain and phase margins when driving large capacitive loads. Figure 55 and Figure 56 show the effects of adding series resistances of 10 Ω , 50 Ω , 100 Ω , 200 Ω , and 500 Ω . The addition of this series resistor has two effects – the first adds a zero to the transfer function and the second reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the improvement in phase margin, equation 1 can be used.

$$\Delta\phi_{m1} = \tan^{-1} \left(2 \times \pi \times \text{UGBW} \times R_{null} \times C_L \right) \quad (1)$$

Where :

- $\Delta\phi_{m1}$ = improvement in phase margin
- UGBW = unity-gain bandwidth frequency
- R_{null} = output series resistance
- C_L = load capacitance

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 58). To use equation 1, UGBW must be approximated from Figure 58.

Using equation 1 alone overestimates the improvement in phase margin as illustrated in Figure 59. The overestimation is caused by the decrease in the frequency of the pole associated with the load, providing additional phase shift and reducing the overall improvement in phase margin.

Using Figure 60, with equation 1 enables the designer to choose the appropriate output series resistance to optimize the design of circuits driving large capacitance loads.

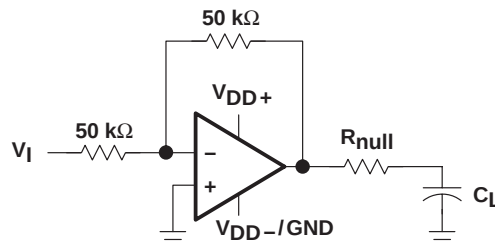


Figure 60. Series-Resistance Circuit

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APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 5) and subcircuit in Figure 61 are generated using the TLV2252 typical electrical and operating characteristics at $T_A = 25^\circ\text{C}$. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 4: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers," *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

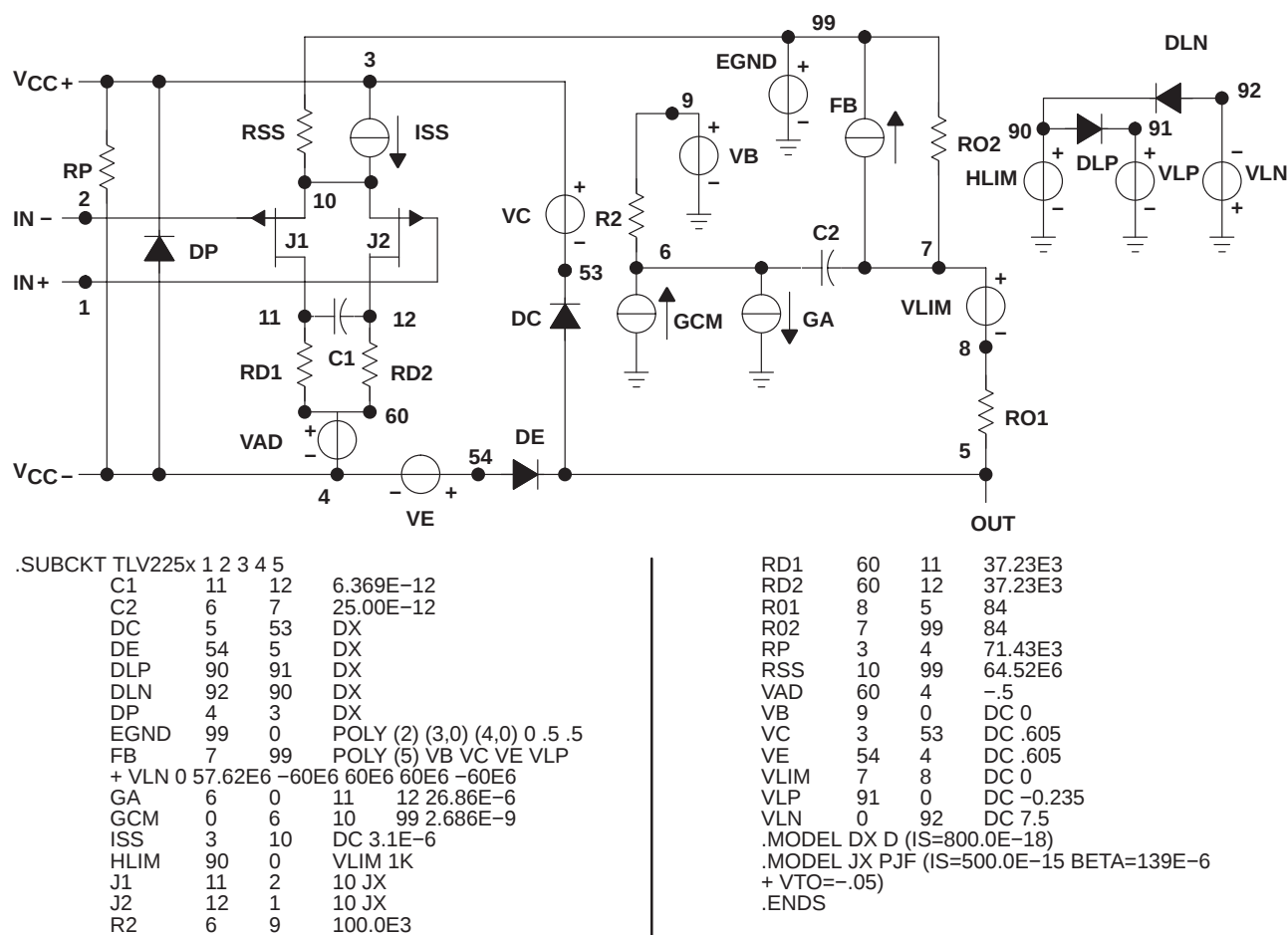


Figure 61. Boyle Macromodel and Subcircuit

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POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TLV2252AQDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2252QDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2254AQDREP	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2254QDREP	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/04651-01UE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/04651-02UE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/04651-03XE	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/04651-04XE	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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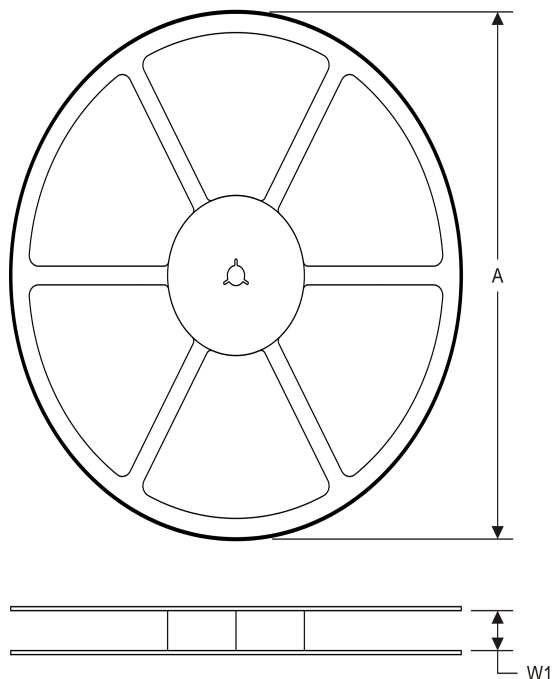
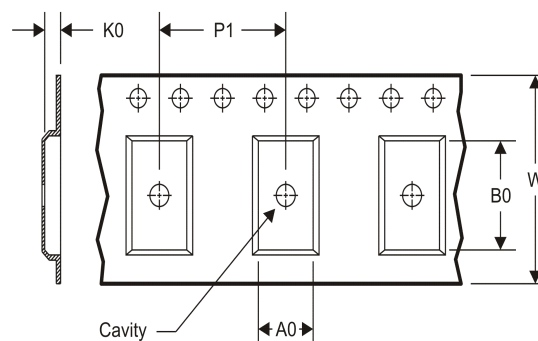
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLV2252-EP, TLV2252A-EP, TLV2254-EP, TLV2254A-EP :

- Catalog: [TLV2252](#), [TLV2252A](#), [TLV2254](#), [TLV2254A](#)
- Automotive: [TLV2252-Q1](#), [TLV2252A-Q1](#), [TLV2254-Q1](#), [TLV2254A-Q1](#)
- Military: [TLV2252M](#), [TLV2252AM](#), [TLV2254M](#), [TLV2254AM](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


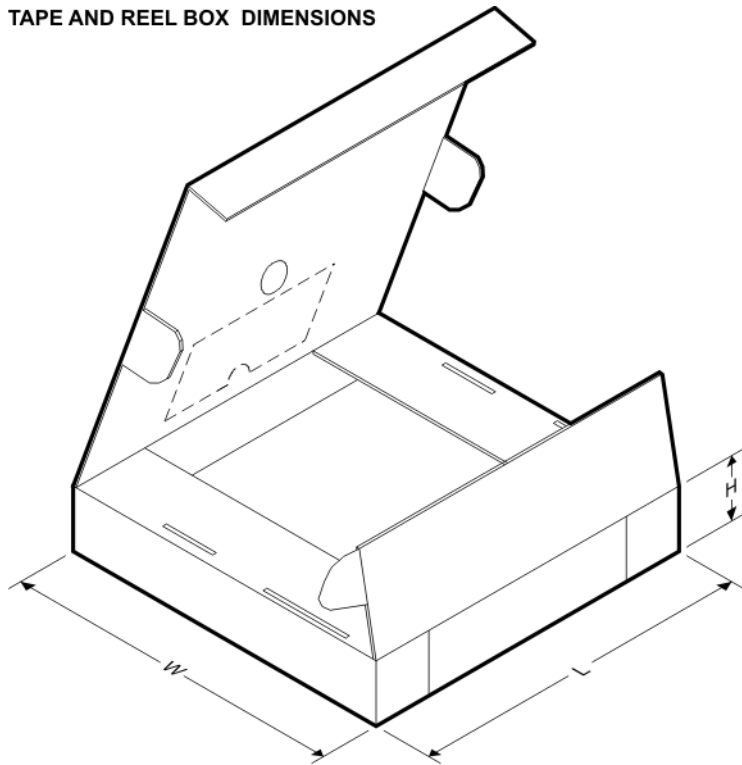
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2252AQDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2252QDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2254AQDREP	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLV2254QDREP	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2252AQDREP	SOIC	D	8	2500	367.0	367.0	35.0
TLV2252QDREP	SOIC	D	8	2500	367.0	367.0	35.0
TLV2254AQDREP	SOIC	D	14	2500	333.2	345.9	28.6
TLV2254QDREP	SOIC	D	14	2500	333.2	345.9	28.6

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



4040047-5/M 06/11

NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14)

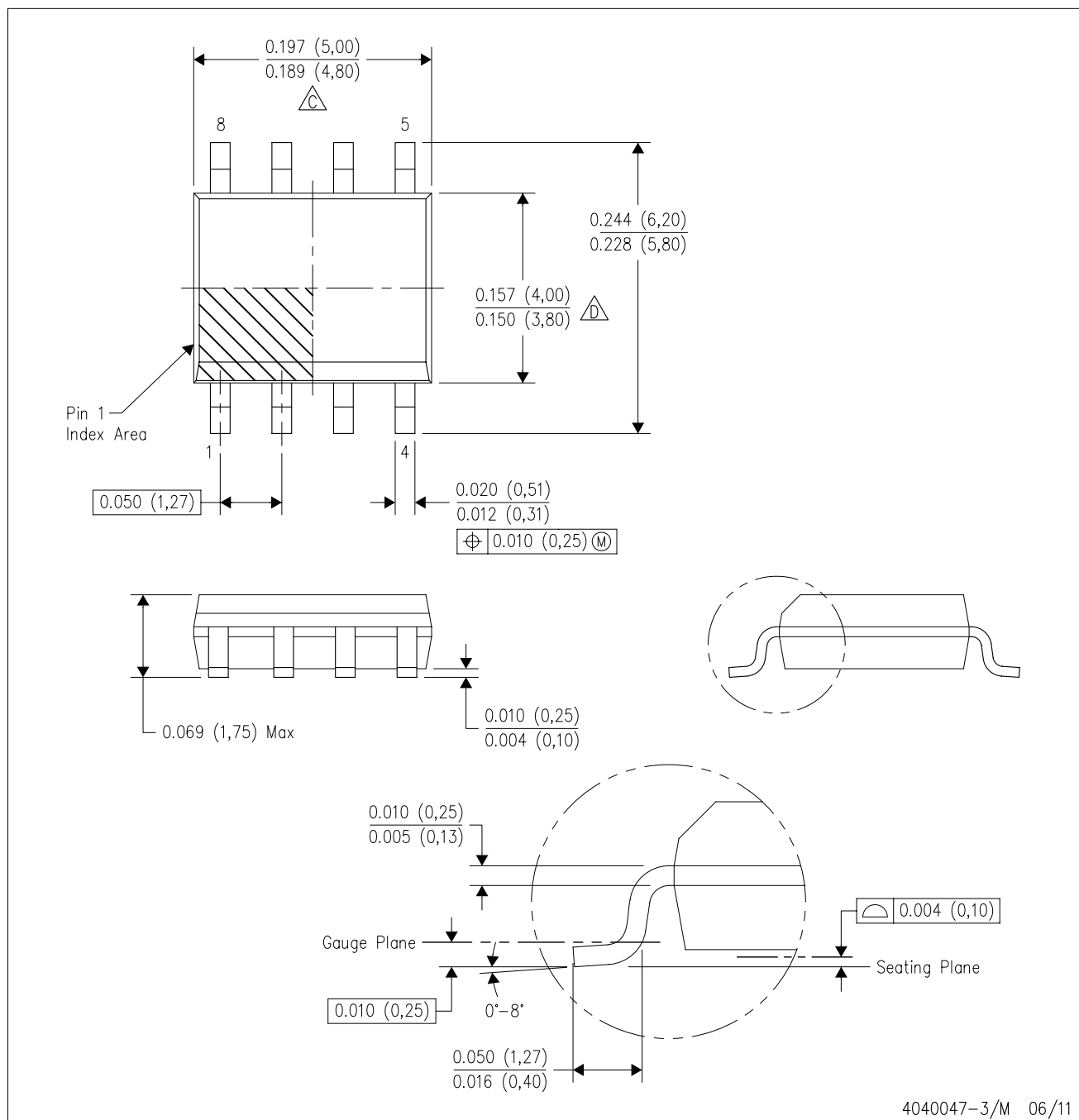
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R-PDSO-G8)

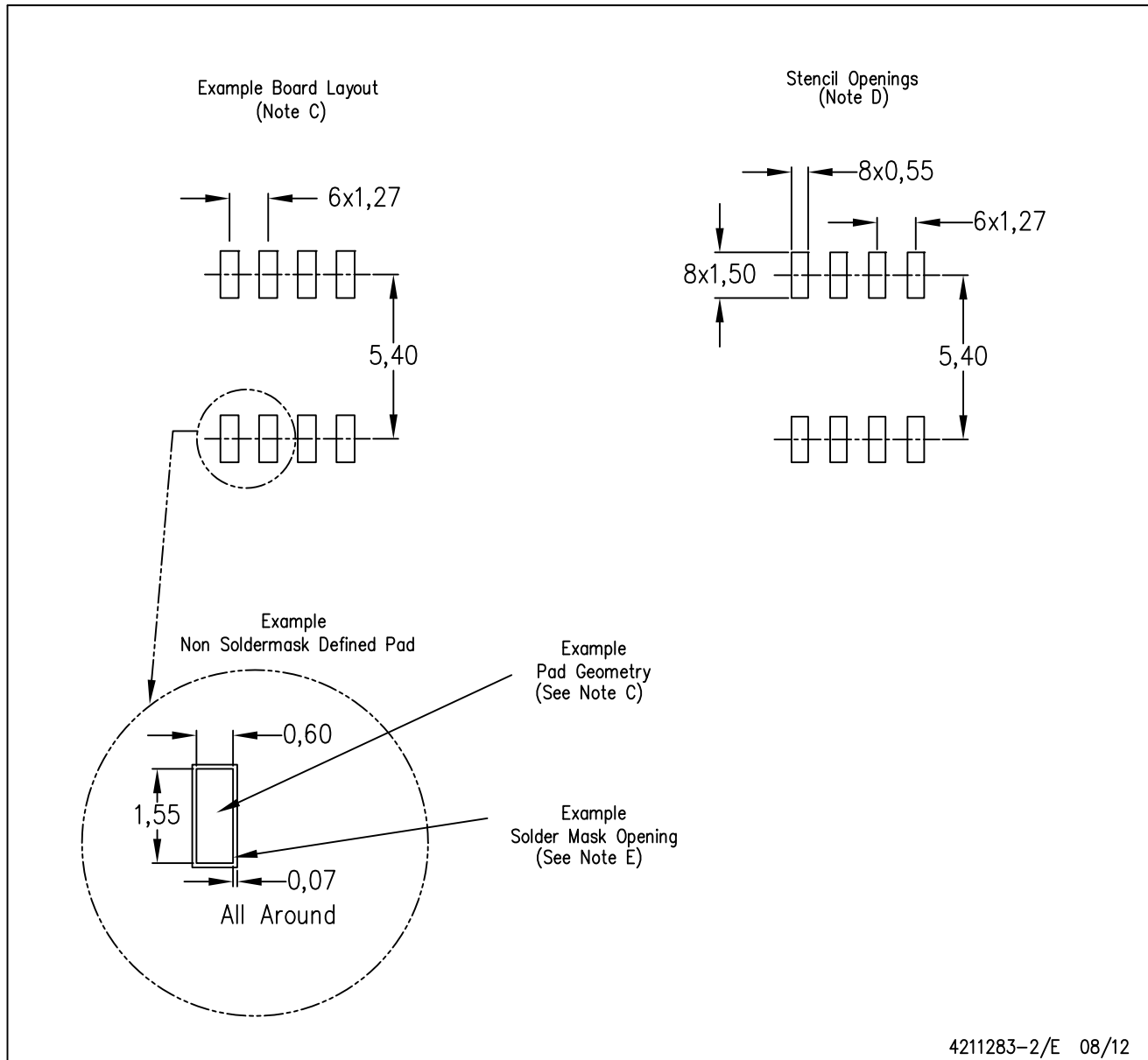
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - $\triangle C$ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - $\triangle D$ Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AA.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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